ISL71840SEH

Radiation Hardened 30V 16-Channel Analog Multiplexer

The ISL71840SEH is a radiation hardened, 16-channel high ESD protected multiplexer fabricated using the Renesas proprietary P6SOI (Silicon On Insulator) process technology to mitigate single-event effects and total ionizing dose. It operates with a dual supply voltage ranging from ±10.8V to ±16.5V. It has a 4-bit address plus an enable pin that can be driven with adjustable logic thresholds to conveniently select one of 16 available channels. An inactive channel is separated from an active channel by a high impedance, which inhibits any interaction between them.

The ISL71840SEH's low r_{ON} allows for improved signal integrity and reduced power losses. The ISL71840SEH is also designed for cold sparing, making it excellent for high reliability applications that have redundancy requirements. It is designed to provide a high impedance to the analog source in a powered off condition, making it easy to add additional backup devices without loading signal sources. The ISL71840SEH also incorporates input analog overvoltage protection, which disables the switch to protect downstream devices.

The ISL71840SEH is available in a 28 Ld CDFP or die form and operates across the extended temperature range of -55°C to +125°C.

A 32-channel version in a 48 Ld CQFP is also available. Refer to the ISL71841SEH datasheet for more information. For a list of differences between the ISL71840SEH and ISL71841SEH, refer to Table 1 on page 3.

Features

- DLA SMD #5962-15219
- Fabricated using P6SOI process technology
  - Provides latch-up immunity
- ESD protection 8kV (HBM)
- Rail-to-rail operation
- Overvoltage protection
- Low r_{ON}. . . . . <500Ω (typical)
- Flexible split rail operation
  - Positive supply above GND (V^+) . . . . . +10.8V to +16.5V
  - Negative supply below GND (V^-) . . . . . -10.8V to -16.5V
- Adjustable logic threshold control with VREF pin
- Cold sparing capable (from ground). . . . . ±25V
- Analog overvoltage range (from ground). . . . . ±35V
- Off switch leakage . . . . . 100nA (maximum)
- Transition times (t_R, t_F) . . . . . 500ns (typical)
- Break-before-make switching
- Grounded metal lid (internally connected)
- Operating temperature range. . . . . -55°C to +125°C
- Radiation acceptance testing
  - High dose rate (50-300rad(Si)/s). . . . . 100krad(Si)
  - Low dose rate (0.01rad(Si)/s) . . . . . 100krad(Si)

NOTE: Product capability established by initial characterization. All subsequent lots are assurance tested to 50krad (0.01rad(Si)/s) wafer-by-wafer.

- SEE hardness (see SEE report for details)
  - SEB LET_{TH} . . . . . 86.4MeV•cm^2/mg

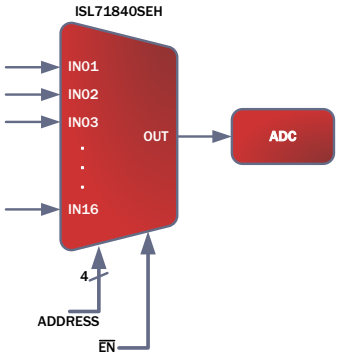

FIGURE 1. TYPICAL APPLICATION

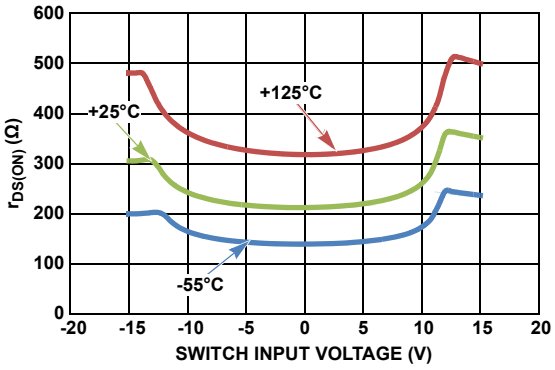

FIGURE 2. $r_{DS(ON)}$ vs POWER SUPPLY ACROSS SWITCH INPUT COMMON-MODE VOLTAGE AT +25°C

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Ordering Information

ORDERING/SMD NUMBER (Note 2)	PART NUMBER (Note 1)	RADIATION HARDNESS (Total Ionizing Dose)	PACKAGE DESCRIPTION (RoHS COMPLIANT)	PKG. DWG. #	TEMP RANGE
5962R1521901VXC	ISL71840SEHVF	HDR to 100krad(Si), LDR to 100krad(Si)	28 LD CDFP	K28.A	-55 to +125°C
5962R1521901V9A	ISL71840SEHVX (Note 3)		Die	N/A	
N/A	ISL71840SEHF/PROTO (Note 4)	N/A	28 LD CDFP	K28.A	
N/A	ISL71840SEHX/SAMPLE (Notes 3, 4)		Die	N/A	
N/A	ISL71840SEHEV1Z (Note 5)	Evaluation Board			

NOTES:

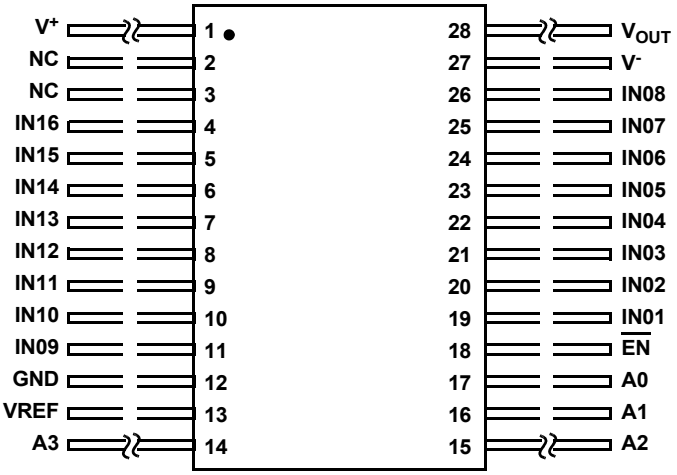
1. These Pb-free Hermetic packaged products employ 100% Au plate - e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations.
2. Specifications for Rad Hard QML devices are controlled by the Defense Logistics Agency Land and Maritime (DLA). The SMD numbers listed must be used when ordering.
3. Die product tested at T_A = + 25°C. The wafer probe test includes functional and parametric testing sufficient to make the die capable of meeting the electrical performance outlined in “Electrical Specifications (±15V)” on page 5 and “Electrical Specifications (±12V)” on page 8.
4. The /PROTO and /SAMPLE are not rated or certified for Total Ionizing Dose (TID) or Single Event Effect (SEE) immunity. These parts are intended for engineering evaluation purposes only. The /PROTO parts meet the electrical limits and conditions across temperature specified in the DLA SMD and are in the same form and fit as the qualified device. The /SAMPLE parts are capable of meeting the electrical limits and conditions specified in the DLA SMD. The /SAMPLE parts do not receive 100% screening across temperature to the DLA SMD electrical limits. These part types do not come with a Certificate of Conformance because they are not DLA qualified devices.
5. Evaluation board uses the /PROTO parts. The /PROTO parts are not rated or certified for Total Ionizing Dose (TID) or Single Event Effect (SEE) immunity.

TABLE 1. TABLE OF DIFFERENCES

SPECIFICATION	ISL71840SEH	ISL71841SEH
Number of Channels	16	32
Supply Current (I+/I-)	350µA (maximum)	400µA (maximum)
Output Leakage (+125°C)	60nA (maximum)	120nA (maximum)

Pin Configuration

(28 LD CDFP)
TOP VIEW



Pin Descriptions

PIN NAME	PIN NUMBER	DESCRIPTION
V_{OUT}	28	Output for multiplexer (see Circuit 1 in Figure 3)
V^+	1	Positive power supply (see Circuit 3 in Figure 3)
V^-	27	Negative power supply (see Circuit 4 in Figure 3)
NC	2, 3	Not electrically connected
INx	4, 5, 6, 7, 8, 9, 10, 11, 19, 20, 21, 22, 23, 24, 25, 26	Input for multiplexer (see Circuit 2 in the following figure)
Ax	14, 15, 16, 17	Address lines for multiplexer (see Circuit 3 in Figure 3)
$\overline{EN}$	18	Enable control for multiplexer (active low, see Circuit 3 in Figure 3)
VREF	13	Reference voltage used to set logic thresholds (see Circuit 3 in Figure 3)
GND	12	Ground
LID	N/A	Package lid is internally connected to GND (Pin 12)

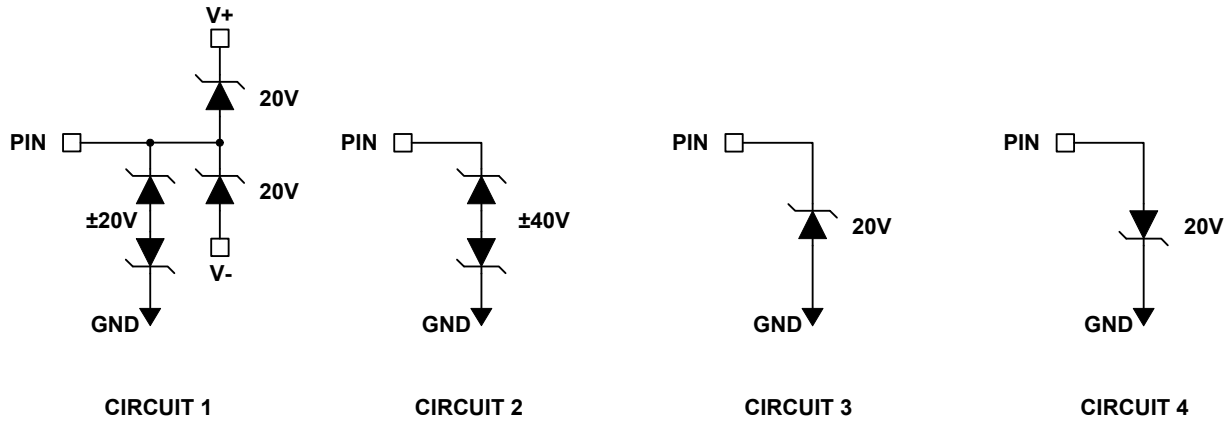


FIGURE 3. ESD CIRCUITS

Absolute Maximum Ratings

Positive Supply Voltage Above GND (V^+) (Note 8) . . . . . +20V
Negative Supply Voltage Below GND (V^-) (Note 8) . . . . . -20V
Maximum Supply Voltage Differential (V^+ to V^-) (Note 8) 40V
Maximum Current Through Selected Switch. 10mA
Analog Input Voltage (INx)
From GND (Note 8). . . . . ±35V
Digital Input Voltage Range ($\overline{EN}$, Ax) . . . . . GND - 0.3V to +16.5V
VREF to GND (Note 8). . . . . +16.5V
ESD Tolerance
Human Body Model (Tested per MIL-STD-883 TM 3015) 8kV
Charged Device Model (Tested per JESD22-C101D) 250V
Machine Model (Tested per JESD22-A115-A) 250V

Thermal Information

Thermal Resistance (Typical)	θ_{JA} (°C/W)	θ_{JC} (°C/W)
28 Ld CDFP (Notes 6, 7)	48	4

Storage Temperature Range. . . . . -65°C to +150°C

Recommended Operating Conditions

Ambient Operating Temperature Range . . . . . -55°C to +125°C
Maximum Operating Junction Temperature . . . . . +150°C
Positive Supply Voltage Above GND (V^+) . . . . . +10.8V to +16.5V
Negative Supply Voltage Below GND (V^-). . . . . -10.8V to -16.5V
Supply Voltage Differential (V^+ to V^-) . . . . . 21.6V to 33V
VREF to GND . . . . . 4.5V to 5.5V

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

NOTES:

6. θ_{JA} is measured with the component mounted on a high-effective thermal conductivity test board in free air. Refer to TB379 for details.
7. For θ_{JC}, the "case temp" location is the center of the package underside.
8. Tested in a heavy ion environment at LET = 86.3MeV • cm^2/mg at +125°C.

Electrical Specifications (±15V)

V^+ = 15V, V^- = -15V, V_{AH} = 4V, V_{AL} = 0.8V, V_{REF} = $V_{\overline{EN}}$ = 5V, T_A = +25°C, unless otherwise noted. **Boldface limits apply across the operating temperature range, -55°C to +125°C or across a total ionizing dose of 300krad(Si) with exposure of a high dose rate of 50 to 300krad(Si)/s or a total ionizing dose of 50krad(Si) with exposure at a low dose rate of <10mrad(Si)/s.**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN (Note 9)	TYP	MAX (Note 9)	UNIT
Analog Input Signal Range	V_S		V^-	-	V^+	V
Channel ON-Resistance	r_{ON}	V± = ±15.0V, ±16.5V, $V_{\overline{EN}}$ = 0V, I_{OUT} = -1mA, V_{IN} = +5V, -5V	-	-	**500**	Ω
		V± = ±15.0V, ±16.5V, $V_{\overline{EN}}$ = 0V, I_{OUT} = -1mA, V_{IN} = V^+, V^-	-	-	**700**	Ω
r_{ON} Match Between Channels	Δr_{ON}	V_{IN} = +5V, -5V; $V_{\overline{EN}}$ = 0V, I_{OUT} = -1mA	-	10	**20**	Ω
ON-Resistance Flatness	$R_{FLAT(ON)}$	V_{IN} = +5V, -5V, $V_{\overline{EN}}$ = 0V	-	-	**25**	Ω
Switch Off Leakage	$I_{S(OFF)}$	V_{IN} = V^+ - 5V, V± = ±16.5V, All unused inputs are tied to V^- + 5V	-10	-	10	nA
		Post radiation	-100	-	100	nA
		V_{IN} = V^- + 5V, V± = ±16.5V All other inputs = V^+ - 5V T_A = +25°C	-10	-	10	nA
		T_A = +125°C	-20	-	20	nA
		Post radiation	-100	-	100	nA
Switch Off Leakage with Device Powered Off	$I_{S(OFF)\ POWER\ OFF}$	V_{IN} = +25V, V± = $V_{\overline{EN}}$ = V_A = V_{REF} = 0V T_A = +25°C, V± = 0V	-10	-	10	nA
		T_A = -55°C, +125°C	-10	-	80	nA
		Post radiation	-100	-	100	nA
		V_{IN} = -25V, V± = $V_{\overline{EN}}$ = V_A = V_{REF} = 0V T_A = +25°C, V± = 0V	-10	-	10	nA
		T_A = -55°C, +125°C	-80	-	10	nA
		Post radiation	-100	-	100	nA

Electrical Specifications (±15V) $V^+ = 15V, V^- = -15V, V_{AH} = 4V, V_{AL} = 0.8V, V_{REF} = V_{\overline{EN}} = 5V, T_A = +25°C$, unless otherwise noted.

Boldface limits apply across the operating temperature range, -55°C to +125°C or across a total ionizing dose of 300krad(Si) with exposure of a high dose rate of 50 to 300krad(Si)/s or a total ionizing dose of 50krad(Si) with exposure at a low dose rate of <10mrad(Si)/s. (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN (Note 9)	TYP	MAX (Note 9)	UNIT
Switch Off Leakage with Device Powered OPEN	$I_{S(OFF)}$ POWER OPEN	V_{IN} = +25V, $V_{\overline{EN}}$ = V_A = V_{REF} = 0V V± = OPEN, T_A = +25°C	-10	-	10	nA
		T_A = -55°C, +125°C	-10	-	80	nA
		Post radiation	-100	-	100	nA
		V_{IN} = -25V, $V_{\overline{EN}}$ = V_A = V_{REF} = 0V V± = OPEN, T_A = +25°C	-10	-	10	nA
		T_A = -55°C, +125°C	-80	-	10	nA
		Post radiation	-100	-	100	nA
Switch On Leakage Current into the Drain (Overvoltage)	$I_{D(ON)\ OVERVOLT}$	V_{IN} = +35V, V_{OUT} = 0V, $V_{\overline{EN}}$ = 0V, All unused switch inputs = GND, V± = ±16.5V	**-10**	-	**10**	nA
		Post radiation	**-10**	-	**10**	nA
		V_{IN} = -35V, V_{OUT} = 0V, $V_{\overline{EN}}$ = 0V, All unused switch inputs = GND, V± = ±16.5V	**-10**	-	**10**	nA
		Post radiation	**-10**	-	**10**	nA
Switch On Leakage Current into the Source (Overvoltage)	$I_{S(ON)\ OVERVOLT}$	V_{IN} = +35V, V_{OUT} = 0V, $V_{\overline{EN}}$ = 0V, All unused switch inputs = GND, V± = ±16.5V	**1**	250	**500**	µA
		Post radiation	**1**	-	**500**	µA
		V_{IN} = -35V, V_{OUT} = 0V, $V_{\overline{EN}}$ = 0V, All unused switch inputs = GND, V± = ±16.5V	**-10**	-5.5	**-1**	µA
		Post radiation	**-10**	-	**-1**	µA
Switch Off Leakage Current into the Source (Overvoltage)	$I_{S(OFF)\ OVERVOLT}$	V_{IN} = +35V, V_{OUT} = 0V, T_A = +25°C, -55°C All unused switch inputs = GND, V± = ±16.5V	-10	-	10	nA
		T_A = +125°C	-80	-	80	nA
		Post radiation	-750	-	750	nA
		V_{IN} = -35V, V_{OUT} = 0V, T_A = +25°C All unused switch inputs = GND, V± = ±16.5V	-10	-	10	nA
		T_A = -55°C	-2	-	2	µA
		T_A = +125°C	-20	-	20	nA
		Post radiation	-750	-	750	nA
Switch Off Leakage	$I_{D(OFF)}$	V_{OUT} = V^+ - 5V, All inputs = V^- + 5V V± = ±16.5V, T_A = +25°C, -55°C	-10	-	10	nA
		T_A = +125°C	0	-	60	nA
		Post radiation	-80	-	80	nA
		V_{OUT} = V^- + 5V, All inputs = V^+ - 5V V± = ±16.5V, T_A = +25°C, -55°C	-10	-	10	nA
		T_A = +125°C	-60	-	0	nA
		Post radiation	-80	-	80	nA

Electrical Specifications (±15V)

V^+ = 15V, V^- = -15V, V_{AH} = 4V, V_{AL} = 0.8V, V_{REF} = $V_{\overline{EN}}$ = 5V, T_A = +25°C, unless otherwise noted. **Boldface limits apply across the operating temperature range, -55°C to +125°C or across a total ionizing dose of 300krad(Si) with exposure of a high dose rate of 50 to 300krad(Si)/s or a total ionizing dose of 50krad(Si) with exposure at a low dose rate of <10mrad(Si)/s. (Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN (Note 9)	TYP	MAX (Note 9)	UNIT
Switch Off Leakage Current into the Drain (Overvoltage)	$I_{D(OFF)\ OVERVOLT}$	V_{OUT} = 0V, V_{IN} = +35V, V± = ±16.5V All unused inputs are tied to GND	-10	-	10	nA
		Post radiation	-500	-	500	nA
		V_{OUT} = 0V, V_{IN} = -35V, V± = ±16.5V All unused inputs are tied to GND	-10	-	10	nA
		Post radiation	-500	-	500	nA
Switch On Leakage Current into the Source/Drain	$I_{D(ON)}$	V_{IN} = V_{OUT} = V^+ - 5V, $V_{\overline{EN}}$ = 0V, T_A = +25°C, -55°C, All unused inputs = V^- + 5V, V± = ±16.5V	-10	-	10	nA
		T_A = +125°C	0	-	60	nA
		Post radiation	-100	-	100	nA
		V_{IN} = V_{OUT} = V^- + 5V, $V_{\overline{EN}}$ = 0V, T_A = +25°C, -55°C, All unused inputs = V^- + 5V, V± = ±16.5V	-10	-	10	nA
		T_A = +125°C	-60	-	0	nA
		Post radiation	-100	-	100	nA
Logic Input High/Low Voltage	$V_{AH/L}$, $V_{ENH/L}$	V_{REF} = 5.0V	**1.2**	-	**1.6**	V
Input Current with V_{AH}, V_{ENH}	I_{AH}, I_{ENH}	V_A = $V_{\overline{EN}}$ = 4.0V V^+ = 16.5V, V^- = -16.5V	**-100**	-	**100**	nA
Input Current with V_{AL}, V_{ENL}	I_{AL}, I_{ENL}	V_A = $V_{\overline{EN}}$ = 0.8V V^+ = 16.5V, V^- = -16.5V	**-100**	-	**100**	nA
Quiescent Supply Current	I+	V_{REF} = 5.5V, V_{IN} = 0V, V_A = 0.8V, $V_{\overline{EN}}$ = 0.8V, V± = ±15.0V, ±16.5V	-	-	**350**	µA
	I-	V_{REF} = 5.5V, V_{IN} = 0V, V_A = 0.8V, $V_{\overline{EN}}$ = 0.8V, V± = ±15.0V, ±16.5V	**-350**	-	-	µA
Standby Supply Current	I+	V_{REF} = 5.5V, V_{IN} = 0V, V_A = 0.8V, $V_{\overline{EN}}$ = 4.0V, V± = ±15.0V, ±16.5V	-	-	**350**	µA
	I-	V_{REF} = 5.5V, V_{IN} = 0V, V_A = 0.8V, $V_{\overline{EN}}$ = 4.0V, V± = ±15.0V, ±16.5V	**-350**	-	-	µA
Quiescent Supply Current Into V_{REF}	I_{REF}	V_{REF} = 5.5V, V_{IN} = 0V, V_A = 0.8V, $V_{\overline{EN}}$ = 0.8V, V± = ±15.0V, ±16.5V	-	-	**35**	µA
Standby Current Into V_{REF}	$I_{REF(STBY)}$	V_{REF} = 5.5V, V_{IN} = 0V, V_A = 0.8V, $V_{\overline{EN}}$ = 4.0V, V± = ±15.0V, ±16.5V	-	-	**35**	µA
DYNAMIC						
Transition Time	t_{ALH}	Figures 5, 6	-	0.5	**800**	ns
Transition Time	t_{AHL}	Figures 5, 6	-	0.5	**800**	ns
Break-Before-Make Delay	t_{BBM}	Figures 9, 10, T_A = -55°C, +25°C, +125°C	5	50	200	ns
		Post radiation	5	-	400	ns
Enable Turn-On Time	t_{ENABLE}	Figures 7, 8, T_A = -55°C, +25°C, +125°C	-	0.5	600	ns
		Post radiation	-	-	800	ns
Disable Turn-Off Time	$t_{DISABLE}$	Figures 7, 8, T_A = -55°C, +25°C, +125°C	-	0.5	600	ns
		Post radiation	-	-	800	ns
Charge Injection	V_{CTE}	C_L = 100pF, V_{IN} = 0V, Figure 7	-	2	5	pC

Electrical Specifications (±15V) $V^+ = 15V, V^- = -15V, V_{AH} = 4V, V_{AL} = 0.8V, V_{REF} = V_{\overline{EN}} = 5V, T_A = +25°C$, unless otherwise noted.

Boldface limits apply across the operating temperature range, -55°C to +125°C or across a total ionizing dose of 300krad(Si) with exposure of a high dose rate of 50 to 300krad(Si)/s or a total ionizing dose of 50krad(Si) with exposure at a low dose rate of <10mrad(Si)/s. (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN (Note 9)	TYP	MAX (Note 9)	UNIT
OFF Isolation	V_{ISO}	$V_{\overline{EN}} = 4V$, $R_L = 1k\Omega$, f = 200kHz, $C_L = 7pF$, $V_{RMS} = 3V$	75	-	-	dB
Crosstalk	V_{CT}	$V_{\overline{EN}} = 0.8V$, $R_L = 1k\Omega$, f = 200kHz, $C_L = 7pF$, $V_{RMS} = 3V$	47	-	-	dB
Digital Input Capacitance	C_A	f = 1MHz, $V^+ = V^- = 0V$	-	-	**7**	pF
Input Capacitance	$C_{IN(OFF)}$	f = 1MHz, $V^+ = V^- = 0V$	-	-	**5**	pF
Output Capacitance	$C_{OUT(OFF)}$	f = 1MHz, $V^+ = V^- = 0V$	-	-	**50**	pF

Electrical Specifications (±12V) $V^+ = 12V, V^- = -12V, V_{AH} = 4.0V, V_{AL} = 0.8V, V_{REF} = V_{\overline{EN}} = 5.0V, T_A = +25°C$, unless otherwise noted.

Boldface limits apply across the operating temperature range, -55°C to +125°C or across a total ionizing dose of 300krad(Si) with exposure of a high dose rate of 50 to 300krad(Si)/s or a total ionizing dose of 50krad(Si) with exposure at a low dose rate of <10mrad(Si)/s.

PARAMETER	SYMBOL	TEST CONDITIONS	MIN (Note 9)	TYP	MAX (Note 9)	UNIT
Analog Input Signal Range	V_S		V^-		V^+	V
Channel ON-Resistance	r_{ON}	V± = ±10.8V, ±13.2V I_{OUT} = -1mA, V_{IN} = +5V, -5V, $V_{\overline{EN}}$ = 0V	-	-	**500**	Ω
		V± = ±10.8V, ±13.2V I_{OUT} = -1mA, $V_{IN} = V^+, V^-$, $V_{\overline{EN}}$ = 0V	-	-	**700**	Ω
r_{ON} Match Between Channels	Δr_{ON}	V_{IN} = +5V, -5V; I_{OUT} = -1mA, $V_{\overline{EN}}$ = 0V	-	10	**20**	Ω
ON-Resistance Flatness	$R_{FLAT(ON)}$	V_{IN} = +5V, -5V, V± = ±13.2V, $V_{\overline{EN}}$ = 0V	-	-	**25**	Ω
		V_{IN} = +5V, -5V, V± = ±10.8V, $V_{\overline{EN}}$ = 0V T_A = +25°C, -55°C, +125°C	-	-	30	Ω
		V_{IN} = +5V, -5V, V± = ±10.8V, $V_{\overline{EN}}$ = 0V, post radiation	-	-	40	Ω
Quiescent Supply Current	I+	V_{REF} = 5.5V, V_{IN} = 0V, V_A = 0.8V, $V_{\overline{EN}}$ = 0.8V, V± = ±10.8V, ±13.2V	-	-	**350**	µA
	I-	V_{REF} = 5.5V, V_{IN} = 0V, V_A = 0.8V, $V_{\overline{EN}}$ = 0.8V, V± = ±10.8V, ±13.2V	**-350**	-	-	µA
Standby Supply Current	I+	V_{REF} = 5.5V, V_{IN} = 0V, V_A = 0.8V, $V_{\overline{EN}}$ = 4.0V, V± = ±10.8V, ±13.2V	-	-	**350**	µA
	I-	V_{REF} = 5.5V, V_{IN} = 0V, V_A = 0.8V, $V_{\overline{EN}}$ = 4.0V, V± = ±10.8V, ±13.2V	**-350**	-	-	µA
Quiescent Supply Current Into V_{REF}	I_{REF}	V_{REF} = 5.5V, V_{IN} = 0V, V_A = 0.8V, $V_{\overline{EN}}$ = 0.8V, V± = ±10.8V, ±13.2V	-	-	**35**	µA
Standby Current Into V_{REF}	$I_{REF(STBY)}$	V_{REF} = 5.5V, V_{IN} = 0V, V_A = 0.8V, $V_{\overline{EN}}$ = 4.0V, V± = ±10.8V, ±13.2V	-	-	**35**	µA
DYNAMIC						
Transition Time	t_{ALH}	Figures 5, 6	-	0.5	**800**	ns
Transition Time	t_{AHL}	Figures 5, 6	-	0.5	**800**	ns
Break-Before-Make Delay	t_{BBM}	Figures 9, 10, T_A = -55°C, +25°C, +125°C	5	50	200	ns
		Post radiation	-	-	400	ns
Enable Turn-On Time	t_{ENABLE}	Figures 7, 8, T_A = -55°C, +25°C, +125°C	-	0.5	600	ns
		Post radiation	-	-	800	ns

Electrical Specifications (±12V) V^+ = 12V, V^- = -12V, V_{AH} = 4.0V, V_{AL} = 0.8V, V_{REF} = $V_{\overline{EN}}$ = 5.0V, T_A= +25°C, unless otherwise noted. **Boldface limits apply across the operating temperature range, -55°C to +125°C or across a total ionizing dose of 300krad(Si) with exposure of a high dose rate of 50 to 300krad(Si)/s or a total ionizing dose of 50krad(Si) with exposure at a low dose rate of <10mrad(Si)/s. (Continued)**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN (Note 9)	TYP	MAX (Note 9)	UNIT
Disable Turn-Off Time	$t_{DISABLE}$	Figures 7, 8, T_A = -55°C, +25°C, +125°C	-	0.5	600	ns
		Post radiation	-	-	800	ns

NOTE:

9. Compliance to datasheet limits is assured by one or more methods: production test, characterization, and/or design.

TABLE 2. TRUTH TABLE

A3	A2	A1	A0	$\overline{EN}$	"ON" Channel
X	X	X	X	1	None
0	0	0	0	0	1
0	0	0	1	0	2
0	0	1	0	0	3
0	0	1	1	0	4
0	1	0	0	0	5
0	1	0	1	0	6
0	1	1	0	0	7
0	1	1	1	0	8
1	0	0	0	0	9
1	0	0	1	0	10
1	0	1	0	0	11
1	0	1	1	0	12
1	1	0	0	0	13
1	1	0	1	0	14
1	1	1	0	0	15
1	1	1	1	0	16

NOTE:

10. X = Don't care, "1" = Logic High, "0" = Logic Low.

Block Diagram

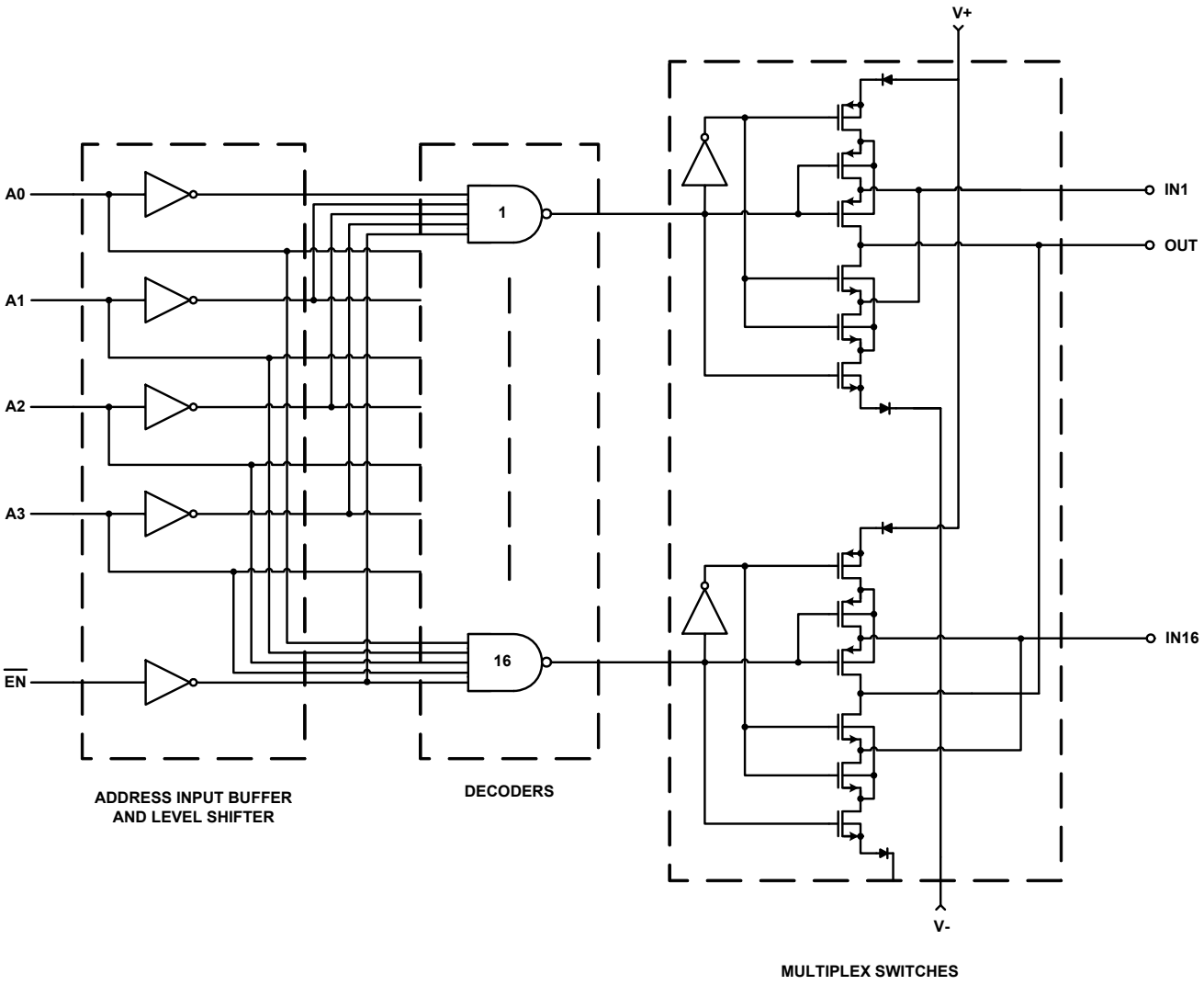


FIGURE 4. BLOCK DIAGRAM

Timing Diagrams

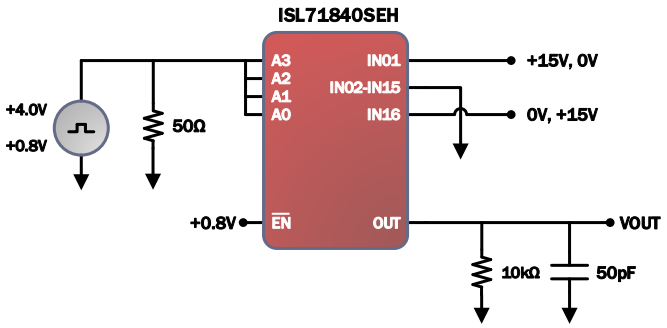


FIGURE 5. ADDRESS TIME TO OUTPUT TEST CIRCUIT

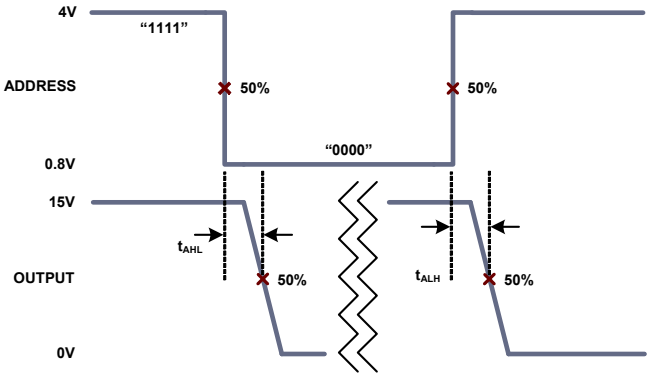


FIGURE 6. ADDRESS TIME TO OUTPUT DIAGRAM

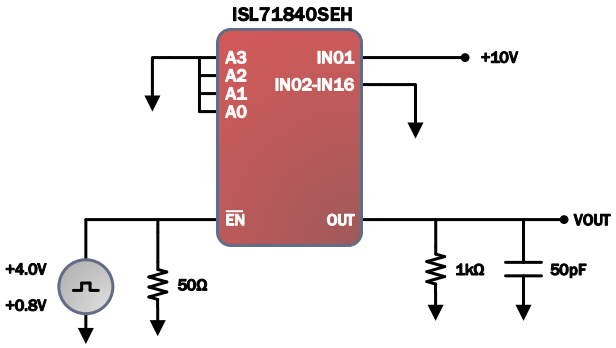


FIGURE 7. TIME TO ENABLE/DISABLE OUTPUT TEST CIRCUIT

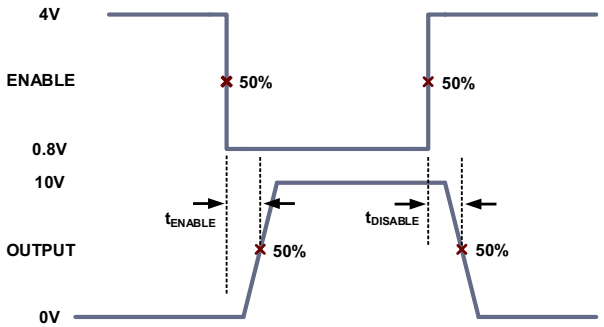


FIGURE 8. TIME TO ENABLE/DISABLE OUTPUT DIAGRAM

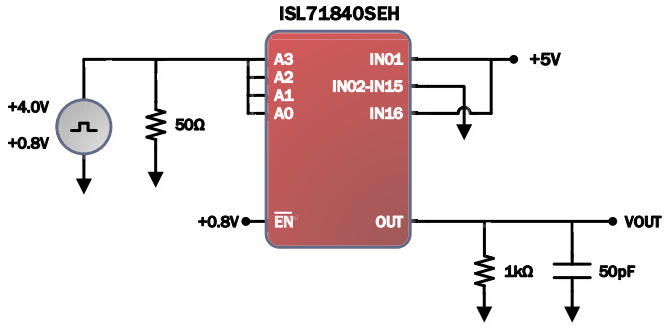


FIGURE 9. BREAK-BEFORE-MAKE TEST CIRCUIT

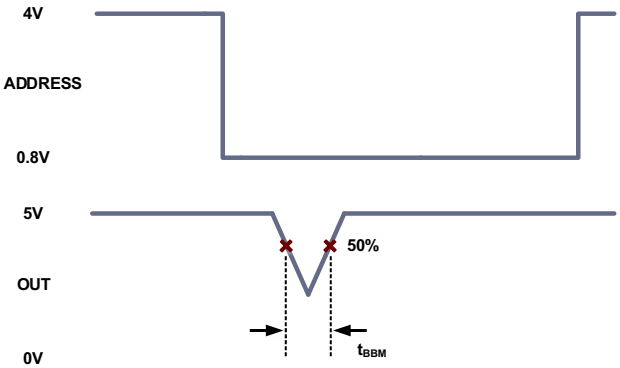


FIGURE 10. BREAK-BEFORE-MAKE DIAGRAM

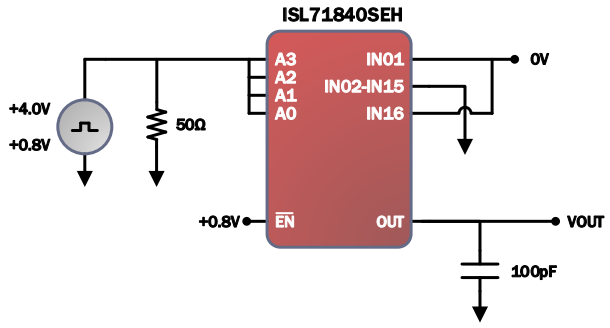


FIGURE 11. CHARGE INJECTION TEST CIRCUIT

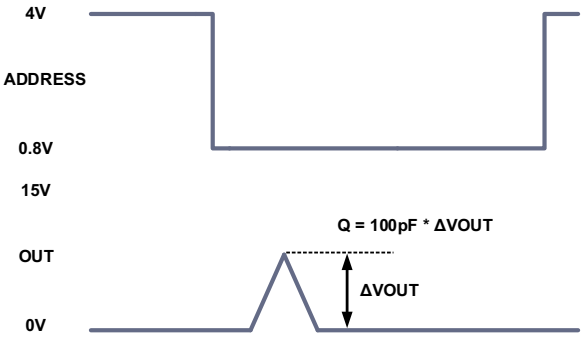


FIGURE 12. CHARGE INJECTION DIAGRAM

Typical Performance Curves

$V\pm = \pm15V$, $V_{CM} = 0V$, R_L = Open, $T_A = +25°C$, unless otherwise specified.

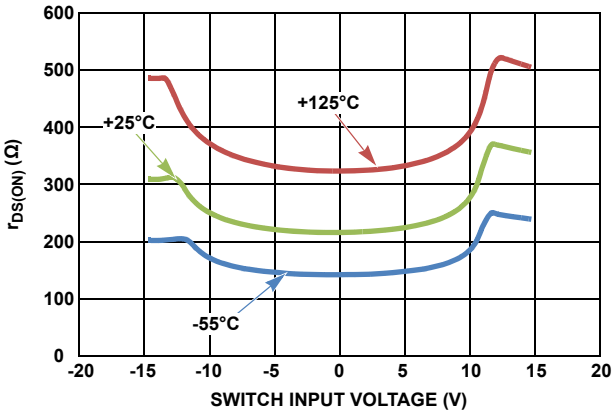


FIGURE 13. $r_{DS(ON)}$ vs VCM (V± = 14.5V)

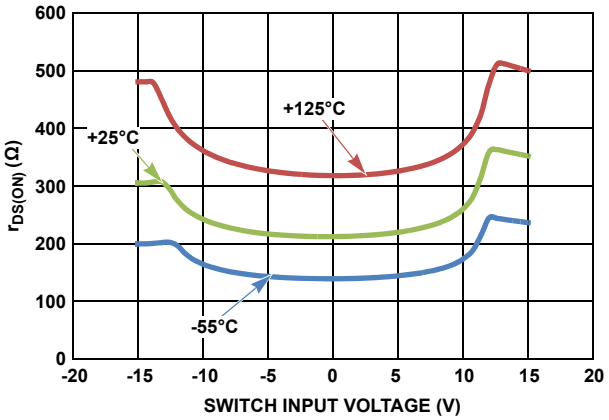


FIGURE 14. $r_{DS(ON)}$ vs VCM (V± = 15.0V)

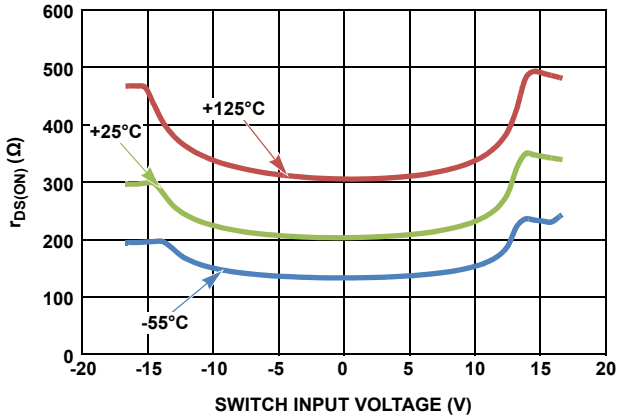


FIGURE 15. $r_{DS(ON)}$ vs VCM (V± = 16.5V)

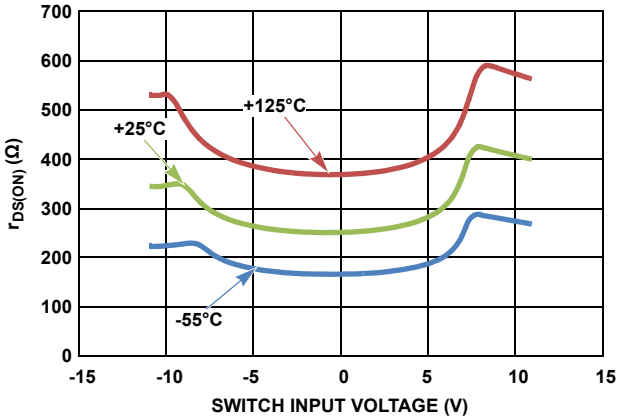


FIGURE 16. $r_{DS(ON)}$ vs VCM (V± = 10.8V)

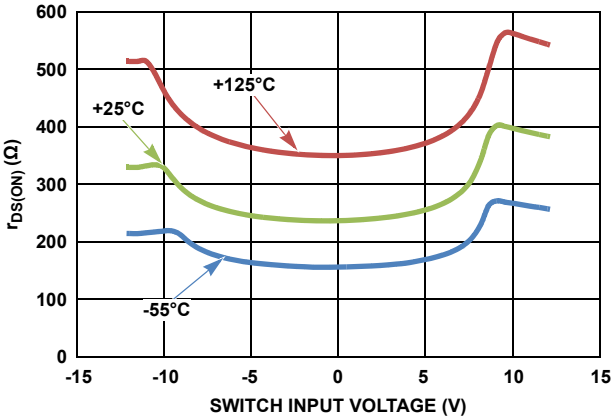


FIGURE 17. $r_{DS(ON)}$ vs VCM (V± = 12.0V)

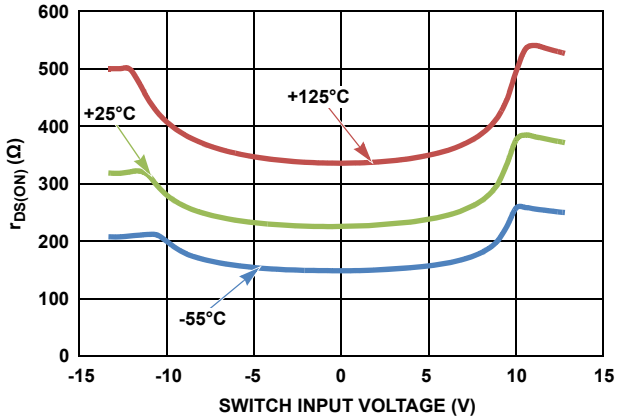


FIGURE 18. $r_{DS(ON)}$ vs VCM (V± = 13.2V)

Typical Performance Curves $V\pm = \pm15V$, $V_{CM} = 0V$, R_L = Open, $T_A = +25°C$, unless otherwise specified. **(Continued)**

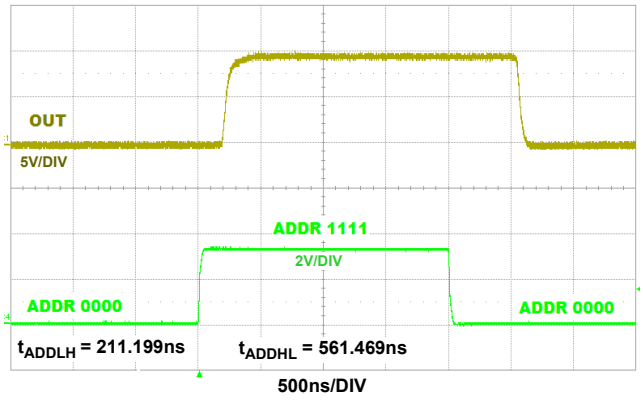


FIGURE 19. TYPICAL ADDRESS TO OUTPUT DELAY ($V\pm = \pm15V$, $+25°C$)

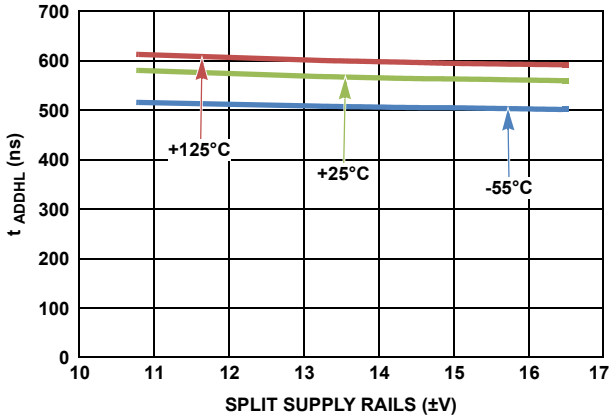


FIGURE 20. ADDRESS TO OUTPUT DELAY (HIGH TO LOW)

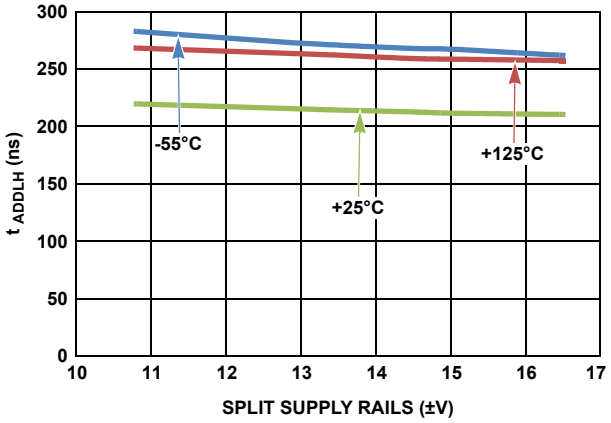


FIGURE 21. ADDRESS TO OUTPUT DELAY (LOW TO HIGH)

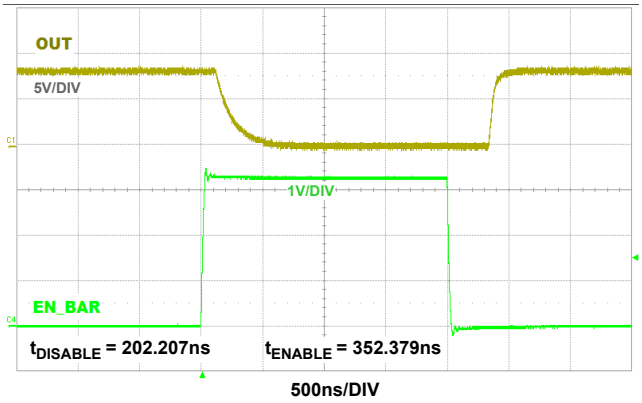


FIGURE 22. TYPICAL ENABLE TO OUTPUT DELAY ($V\pm = \pm15V$, $+25°C$)

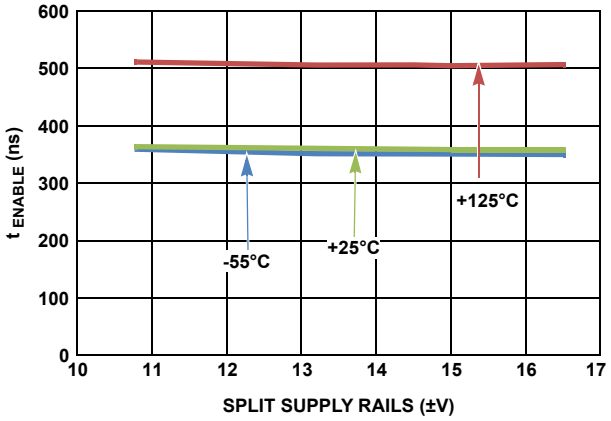


FIGURE 23. ENABLE TO OUTPUT DELAY (LOW TO HIGH)

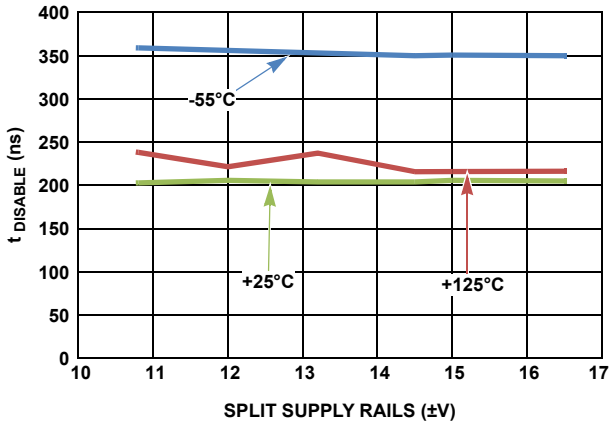


FIGURE 24. DISABLE TO OUTPUT DELAY (LOW TO HIGH)

Typical Performance Curves

$V\pm = \pm15V$, $V_{CM} = 0V$, R_L = Open, $T_A = +25°C$, unless otherwise specified. **(Continued)**

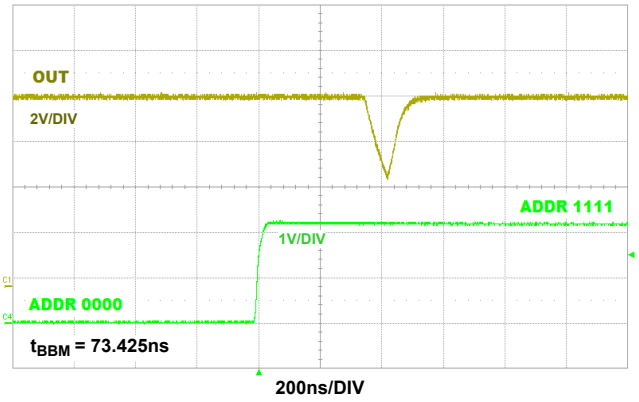


FIGURE 25. TYPICAL BREAK BEFORE MAKE DELAY (V± = 15V, +25°C)

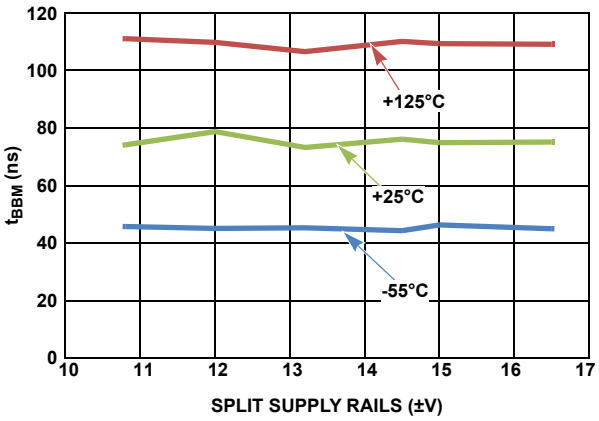


FIGURE 26. BREAK-BEFORE-MAKE DELAY

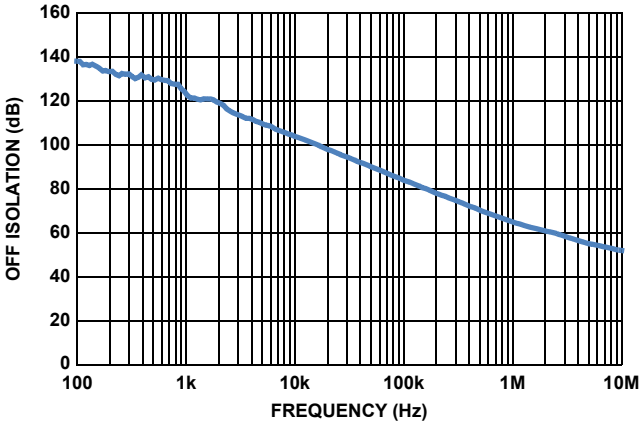


FIGURE 27. OFF ISOLATION (V± = ±15V, R_L = 1kΩ, +25°C)

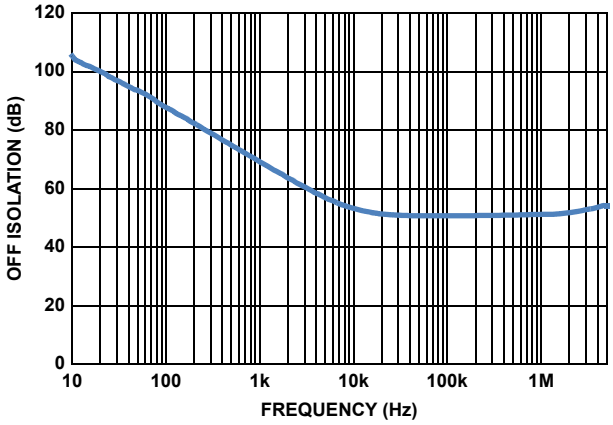


FIGURE 28. OFF ISOLATION (V± = ±15V, R_L = OPEN, +25°C)

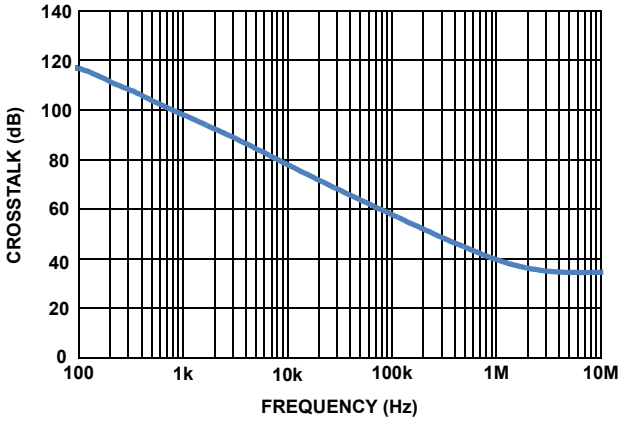


FIGURE 29. CROSSTALK (V± = ±15V, R_L = 1kΩ, +25°C)

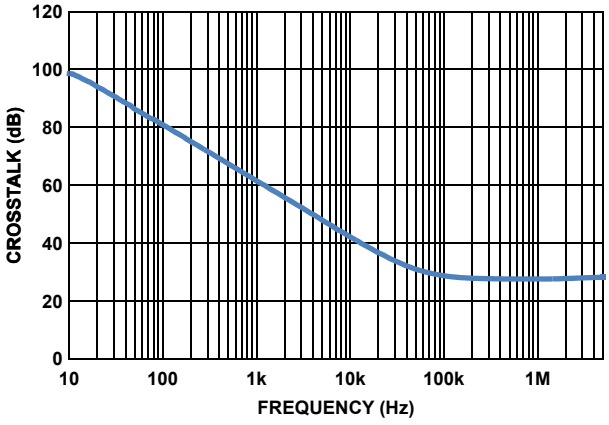


FIGURE 30. CROSSTALK (V± = ±15V, R_L = OPEN, +25°C)

Typical Performance Curves $V\pm = \pm15V$, $V_{CM} = 0V$, R_L = Open, $T_A = +25°C$, unless otherwise specified. **(Continued)**

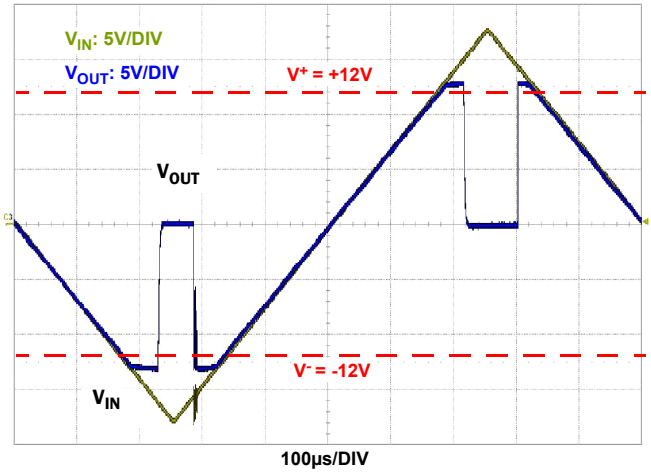


FIGURE 31. OVER/UNDERVOLTAGE PROTECTION (+25°C)

Post High Dose Rate Radiation Characteristics ($V\pm = \pm15V$)

Unless otherwise specified, $V\pm = \pm15V$, $V_{CM} = 0$, $V_O = 0V$, $T_A = +25°C$. This data is typical mean test data post radiation exposure at a high dose rate of 50 to 300rad(Si)/s. This data is intended to show typical parameter shifts due to high dose rate radiation. These are not limits, nor are they guaranteed.

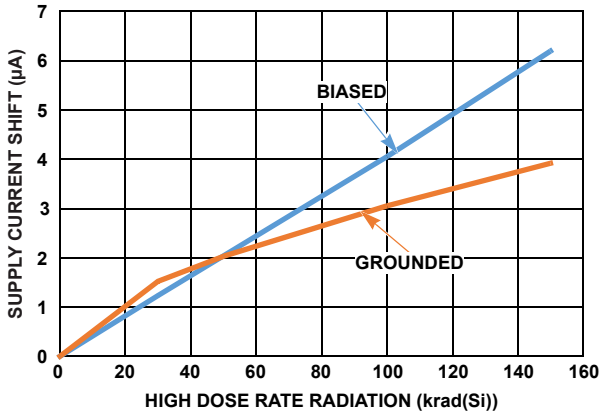


FIGURE 32. ICC SUPPLY CURRENT SHIFT vs HDR RADIATION

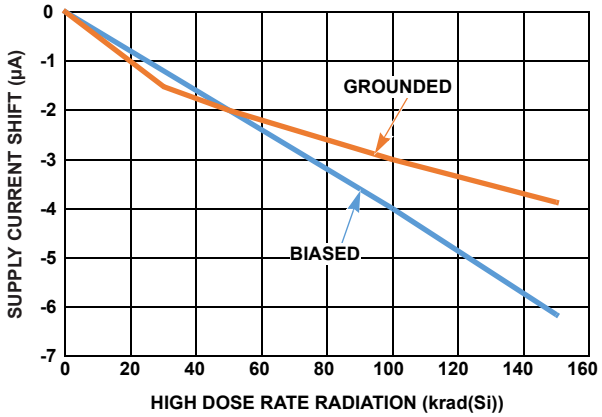


FIGURE 33. IEE SUPPLY CURRENT SHIFT vs HDR RADIATION

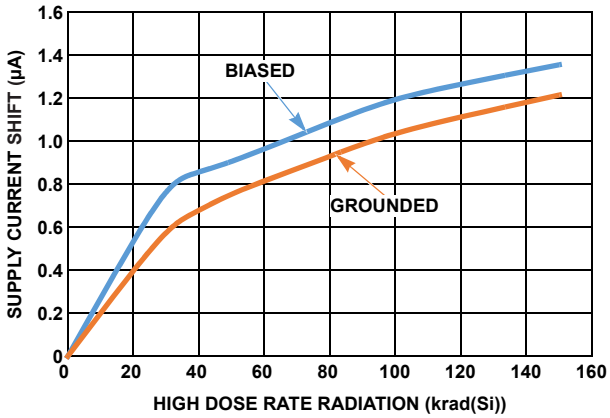


FIGURE 34. I_{REF} SUPPLY CURRENT SHIFT vs HDR RADIATION

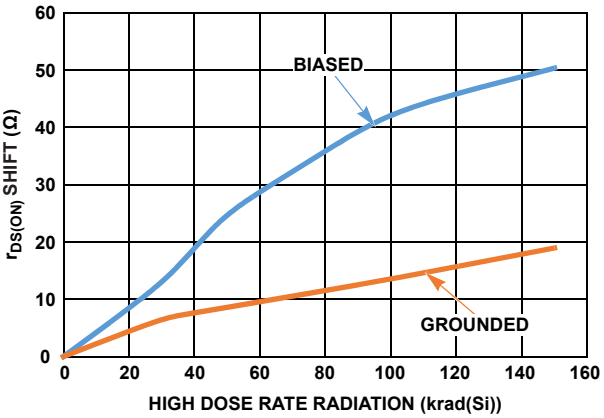


FIGURE 35. $r_{DS(ON)}$ SHIFT ($V_{IN} = V^+$) vs HDR RADIATION

Post High Dose Rate Radiation Characteristics (V± = ±15V)

Unless otherwise specified, V± = ±15V, V_{CM} = 0, V_O = 0V, T_A = +25°C. This data is typical mean test data post radiation exposure at a high dose rate of 50 to 300rad(Si)/s. This data is intended to show typical parameter shifts due to high dose rate radiation. These are not limits, nor are they guaranteed. **(Continued)**

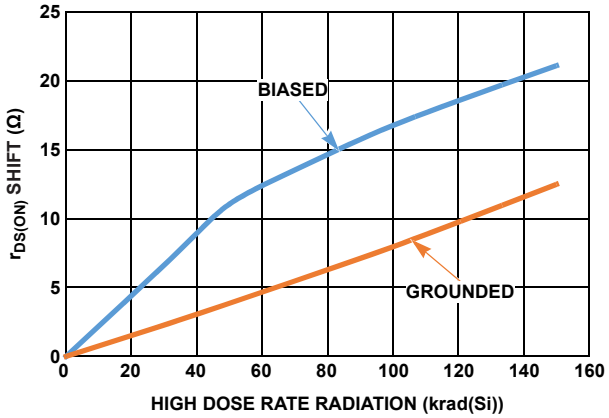


FIGURE 36. $r_{DS(ON)}$ SHIFT (V_{IN} = +5V) vs HDR RADIATION

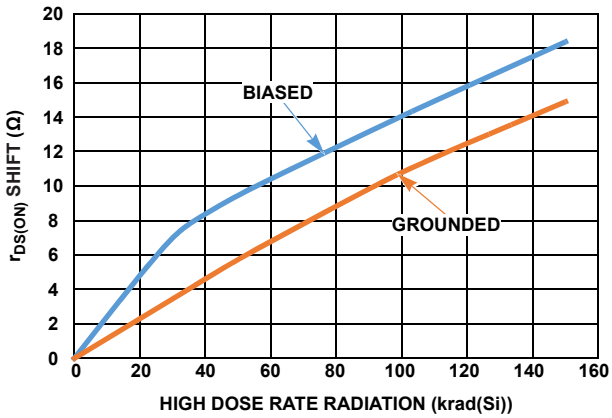


FIGURE 37. $r_{DS(ON)}$ SHIFT (V_{IN} = -5V) vs HDR RADIATION

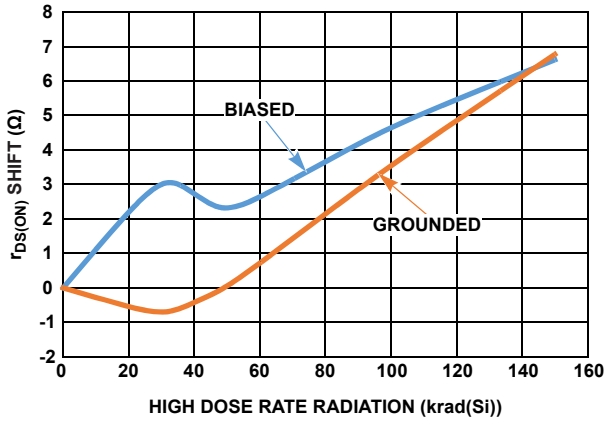


FIGURE 38. $r_{DS(ON)}$ SHIFT (V_{IN} = V^-) vs HDR RADIATION

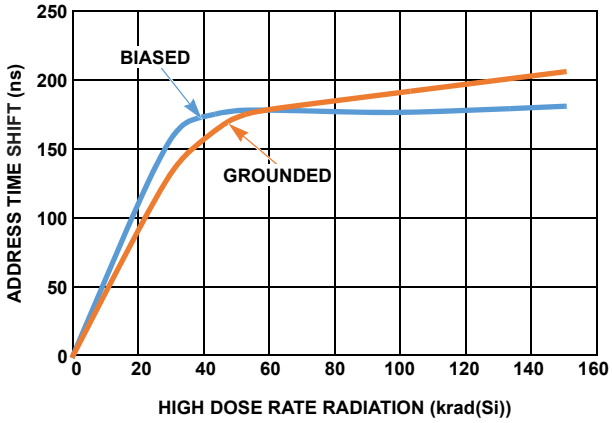


FIGURE 39. t_{ADD} SHIFT (LOW TO HIGH) vs HDR RADIATION

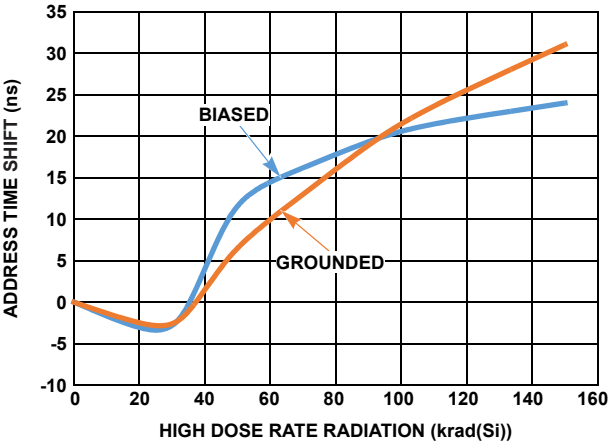


FIGURE 40. t_{ADD} SHIFT (HIGH TO LOW) vs HDR RADIATION

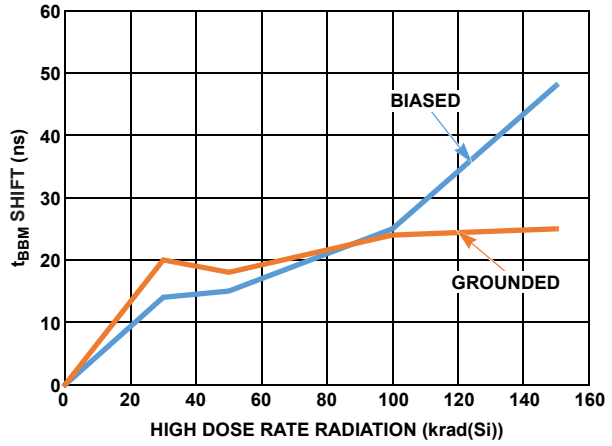


FIGURE 41. t_{BBM} SHIFT vs HDR RADIATION

Post High Dose Rate Radiation Characteristics (V± = ±15V)

Unless otherwise specified, V± = ±15V, V_{CM} = 0, V_O = 0V, T_A = +25°C. This data is typical mean test data post radiation exposure at a high dose rate of 50 to 300rad(Si)/s. This data is intended to show typical parameter shifts due to high dose rate radiation. These are not limits, nor are they guaranteed. **(Continued)**

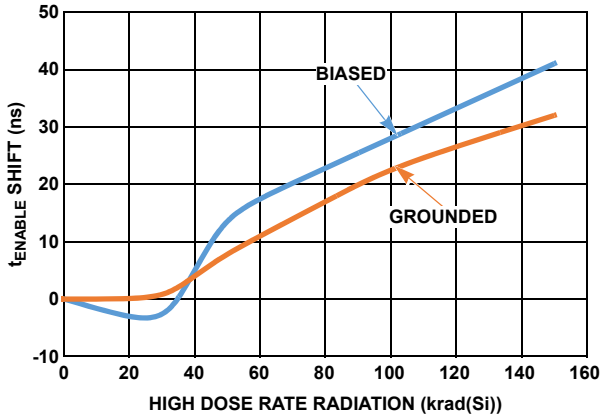


FIGURE 42. t_{ENABLE} SHIFT vs HDR RADIATION

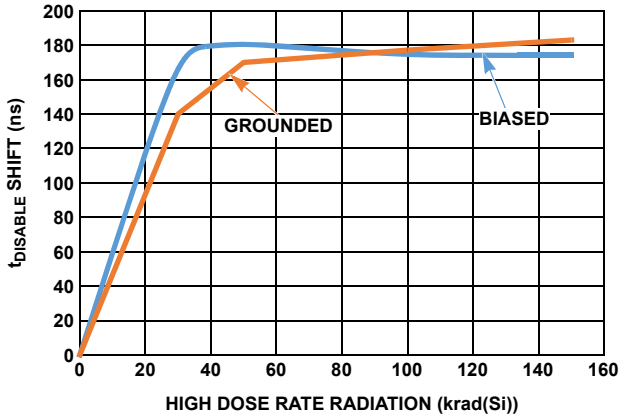


FIGURE 43. $t_{DISABLE}$ SHIFT vs HDR RADIATION

Post High Dose Rate Radiation Characteristics (V± = ±12V)

Unless otherwise specified, V± = ±12V, V_{CM} = 0, V_O = 0V, T_A = +25°C. This data is typical mean test data post radiation exposure at a high dose rate of 50 to 300rad(Si)/s. This data is intended to show typical parameter shifts due to high dose rate radiation. These are not limits, nor are they guaranteed.

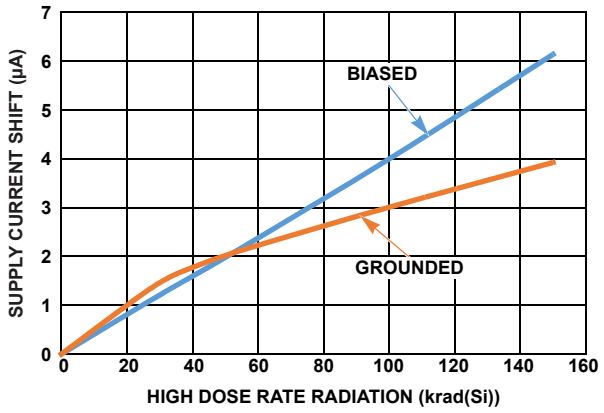


FIGURE 44. ICC SUPPLY CURRENT SHIFT vs HDR RADIATION

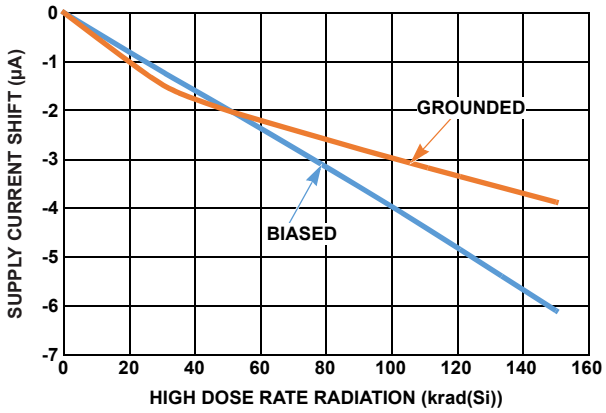


FIGURE 45. IEE SUPPLY CURRENT SHIFT vs HDR RADIATION

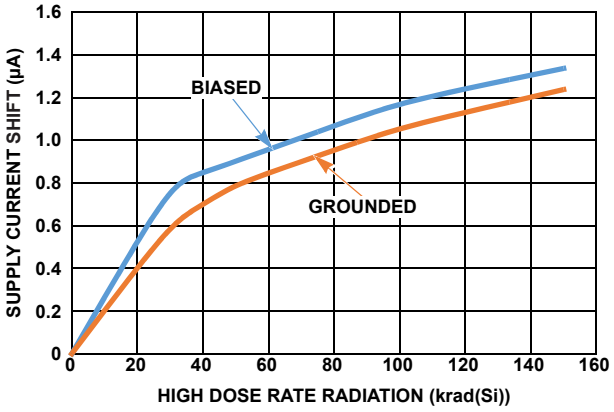


FIGURE 46. I_{REF} SUPPLY CURRENT SHIFT vs HDR RADIATION

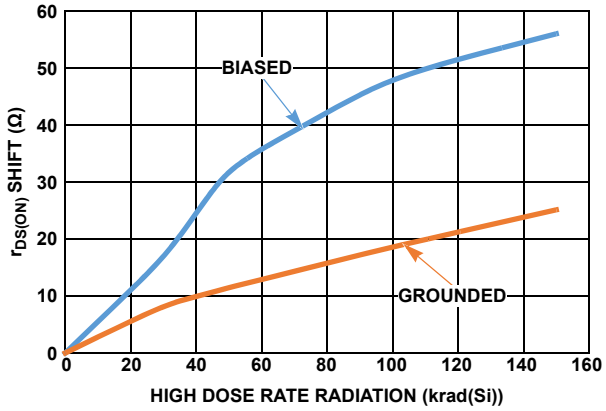


FIGURE 47. $r_{DS(ON)}$ SHIFT (V_{IN} = V^+) vs HDR RADIATION

Post High Dose Rate Radiation Characteristics (V± = ±12V) Unless otherwise specified, V± = ±12V, V_{CM} = 0, V_O = 0V, T_A = +25°C. This data is typical mean test data post radiation exposure at a high dose rate of 50 to 300rad(Si)/s. This data is intended to show typical parameter shifts due to high dose rate radiation. These are not limits, nor are they guaranteed. **(Continued)**

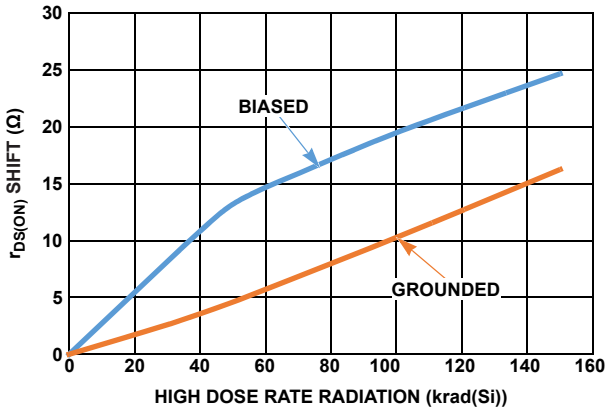


FIGURE 48. $r_{DS(ON)}$ SHIFT (V_{IN} = +5V) vs HDR RADIATION

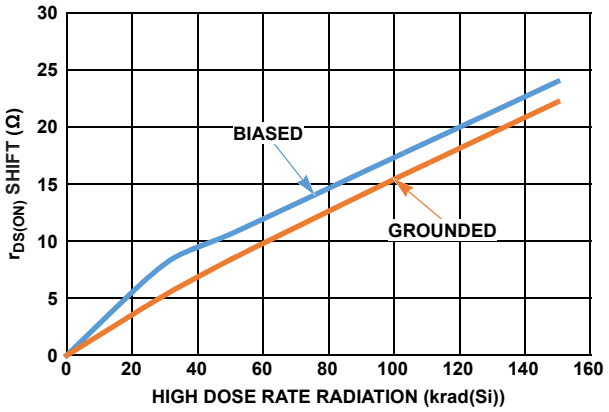


FIGURE 49. $r_{DS(ON)}$ SHIFT (V_{IN} = -5V) vs HDR RADIATION

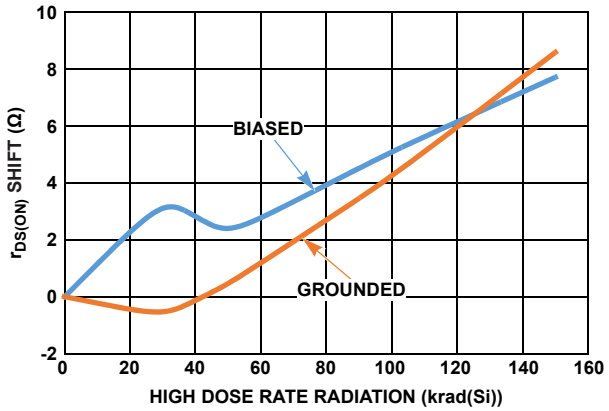


FIGURE 50. $r_{DS(ON)}$ SHIFT (V_{IN} = V^-) vs HDR RADIATION

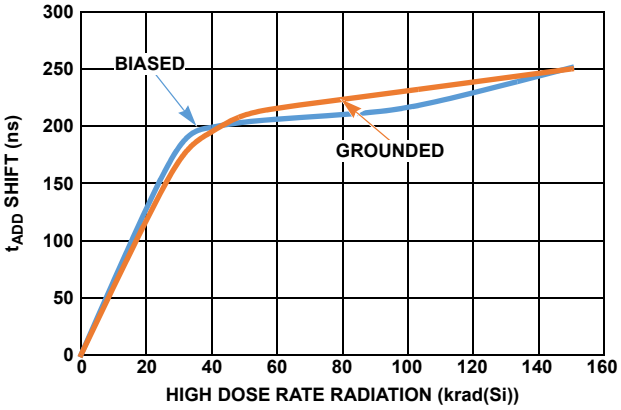


FIGURE 51. t_{ADD} SHIFT (LOW TO HIGH) vs HDR RADIATION

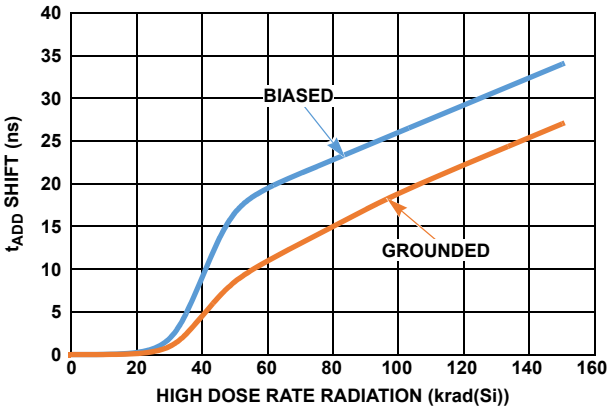


FIGURE 52. t_{ADD} SHIFT (HIGH TO LOW) vs HDR RADIATION

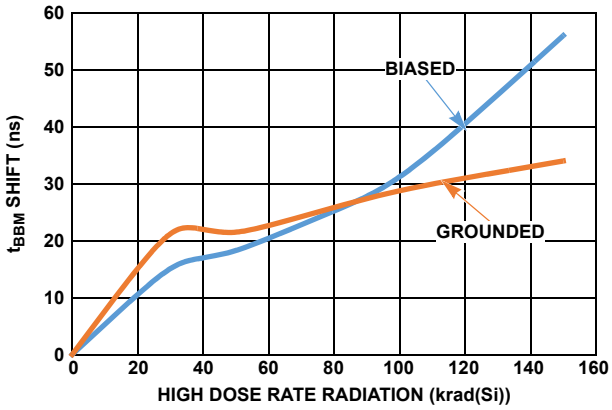


FIGURE 53. t_{BBM} SHIFT vs HDR RADIATION

Post High Dose Rate Radiation Characteristics (V± = ±12V)

Unless otherwise specified, V± = ±12V, V_{CM} = 0, V_O = 0V, T_A = +25°C. This data is typical mean test data post radiation exposure at a high dose rate of 50 to 300rad(Si)/s. This data is intended to show typical parameter shifts due to high dose rate radiation. These are not limits, nor are they guaranteed. **(Continued)**

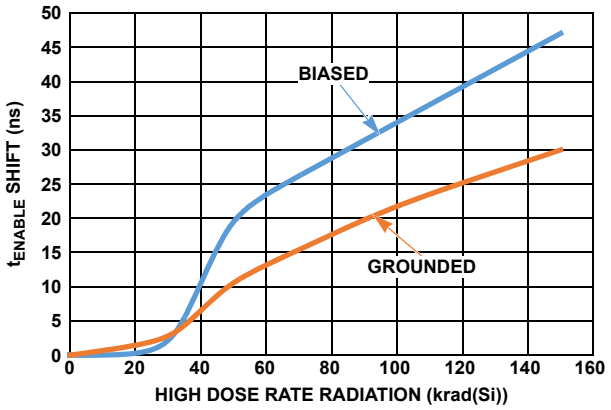


FIGURE 54. t_{ENABLE} SHIFT vs HDR RADIATION

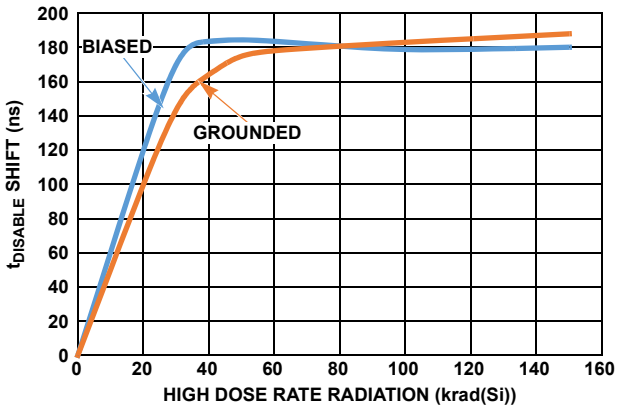


FIGURE 55. $t_{DISABLE}$ SHIFT vs HDR RADIATION

Post Low Dose Rate Radiation Characteristics (V± = ±15V)

Unless otherwise specified, V± = ±15V, V_{CM} = 0, V_O = 0V, T_A = +25°C. This data is typical mean test data post radiation exposure at a low dose rate of <10mrad(Si)/s. This data is intended to show typical parameter shifts due to low dose rate radiation. These are not limits, nor are they guaranteed.

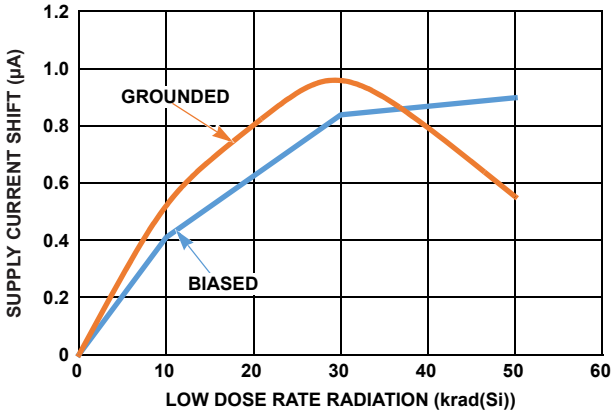


FIGURE 56. I_{CC} SUPPLY CURRENT SHIFT vs LDR RADIATION

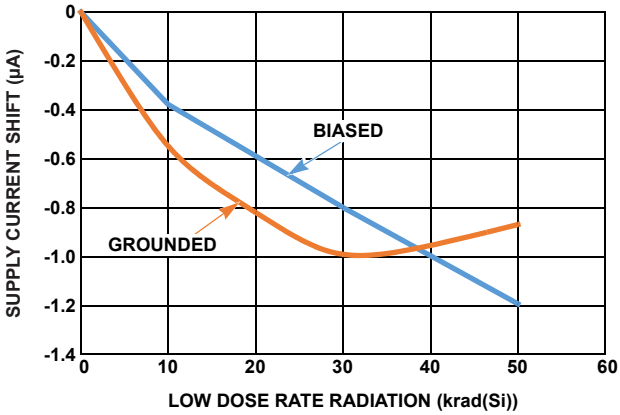


FIGURE 57. I_{EE} SUPPLY CURRENT SHIFT vs LDR RADIATION

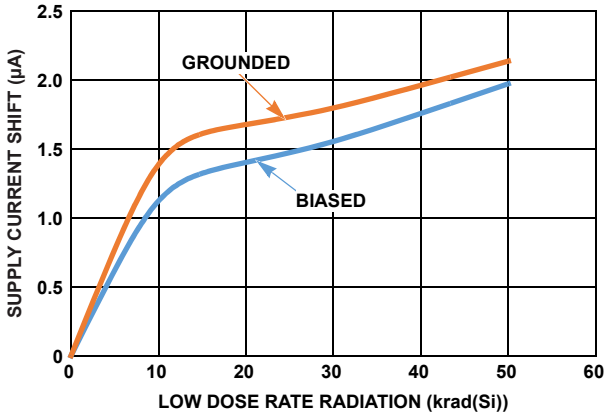


FIGURE 58. I_{REF} SUPPLY CURRENT SHIFT vs LDR RADIATION

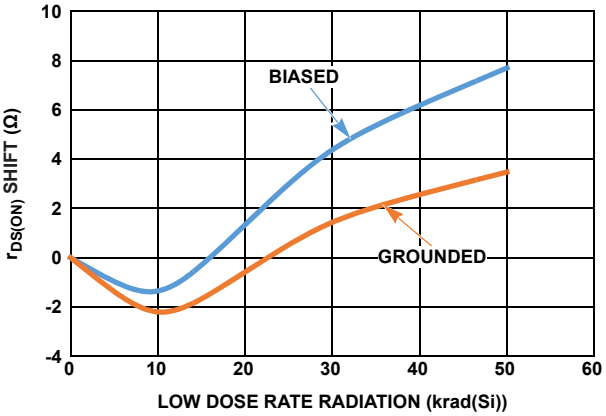


FIGURE 59. $r_{DS(ON)}$ SHIFT (V_{IN} = +5V) vs LDR RADIATION

Post Low Dose Rate Radiation Characteristics ($V\pm$ = ±15V)

Unless otherwise specified, $V\pm$ = ±15V, V_{CM} = 0, V_O = 0V, T_A = +25°C. This data is typical mean test data post radiation exposure at a low dose rate of <10mrad(Si)/s. This data is intended to show typical parameter shifts due to low dose rate radiation. These are not limits, nor are they guaranteed. **(Continued)**

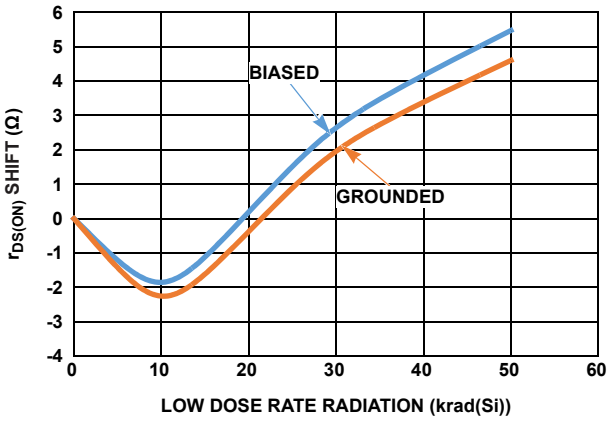


FIGURE 60. $r_{DS(ON)}$ SHIFT (V_{IN} = -5V) vs LDR RADIATION

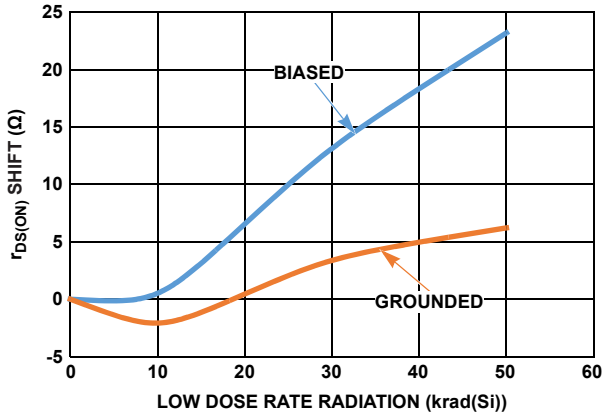


FIGURE 61. $r_{DS(ON)}$ SHIFT (V_{IN} = V^+) vs LDR RADIATION

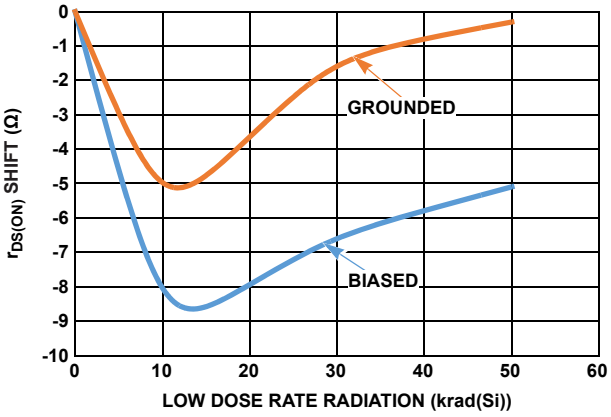


FIGURE 62. $r_{DS(ON)}$ SHIFT (V_{IN} = V^-) vs LDR RADIATION

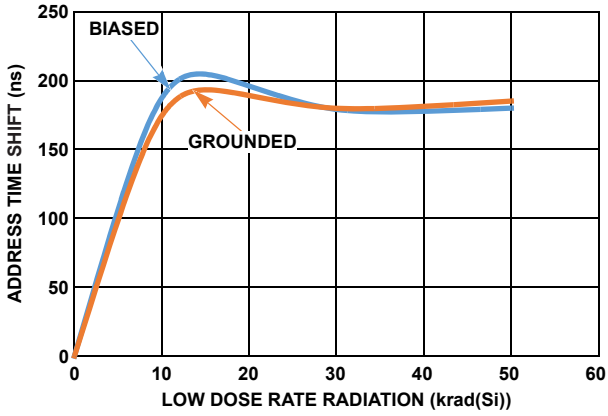


FIGURE 63. t_{ADD} SHIFT (LOW TO HIGH) vs LDR RADIATION

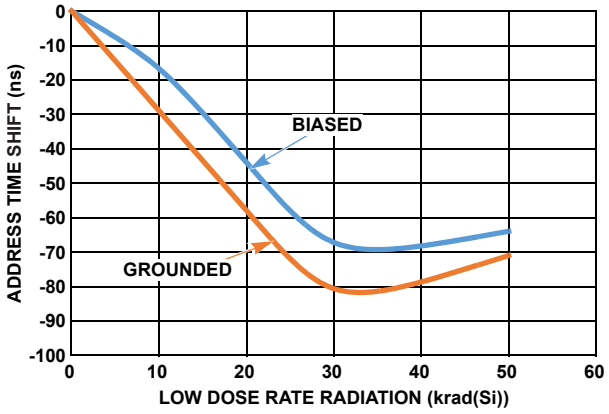


FIGURE 64. t_{ADD} SHIFT (HIGH TO LOW) vs LDR RADIATION

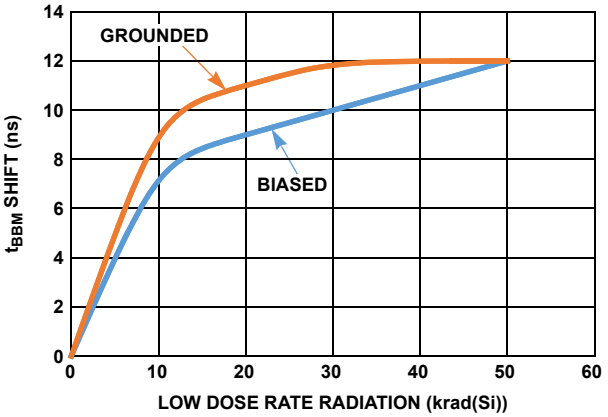


FIGURE 65. t_{BBM} SHIFT vs LDR RADIATION

Post Low Dose Rate Radiation Characteristics (V± = ±15V)

Unless otherwise specified, V± = ±15V, V_{CM} = 0, V_O = 0V, T_A = +25°C. This data is typical mean test data post radiation exposure at a low dose rate of <10mrad(Si)/s. This data is intended to show typical parameter shifts due to low dose rate radiation. These are not limits, nor are they guaranteed. **(Continued)**

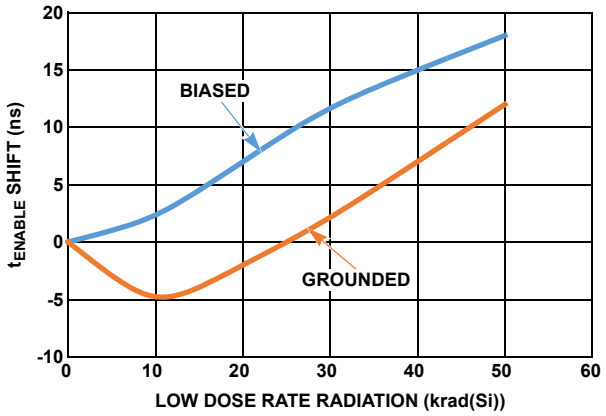


FIGURE 66. t_{ENABLE} SHIFT vs LDR RADIATION

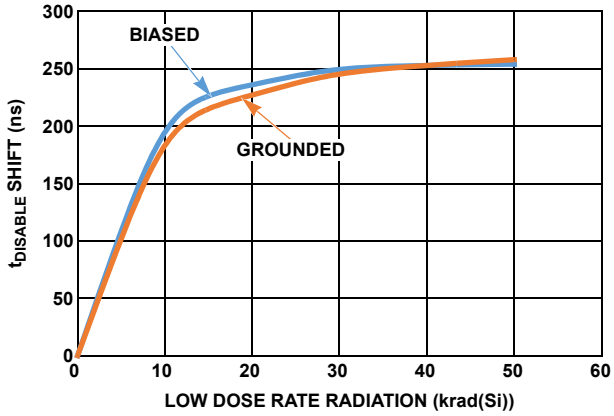


FIGURE 67. $t_{DISABLE}$ SHIFT vs LDR RADIATION

Post Low Dose Rate Radiation Characteristics (V± = ±12V)

Unless otherwise specified, V± = ±12V, V_{CM} = 0,V_O = 0V, T_A = +25°C. This data is typical mean test data post radiation exposure at a low dose rate of <10mrad(Si)/s. This data is intended to show typical parameter shifts due to low dose rate radiation. These are not limits, nor are they guaranteed.

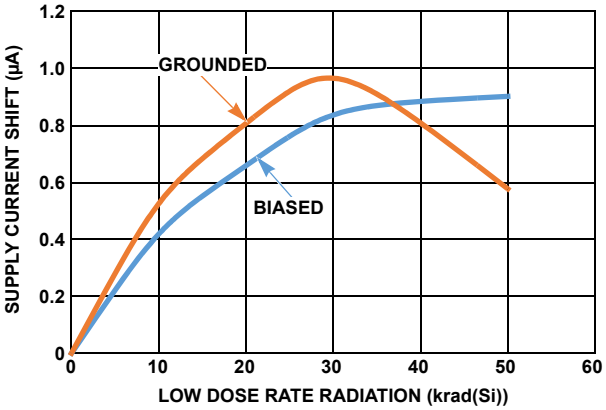


FIGURE 68. I_{CC} SUPPLY CURRENT SHIFT vs LDR RADIATION

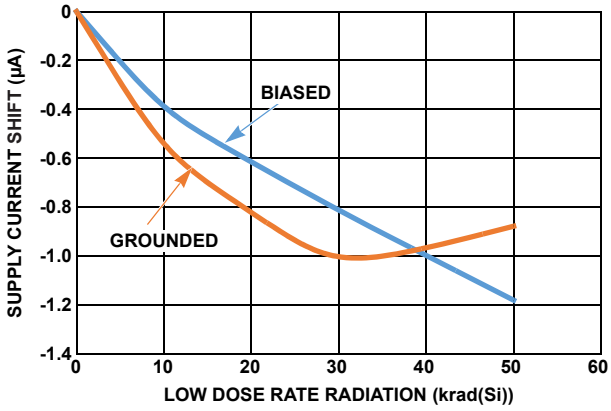


FIGURE 69. I_{EE} SUPPLY CURRENT SHIFT vs LDR RADIATION

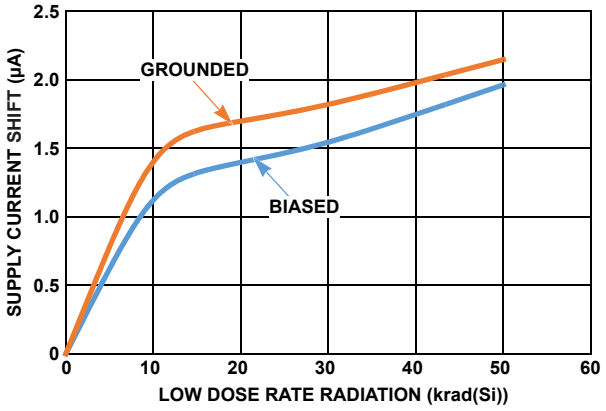


FIGURE 70. I_{REF} SUPPLY CURRENT SHIFT vs LDR RADIATION

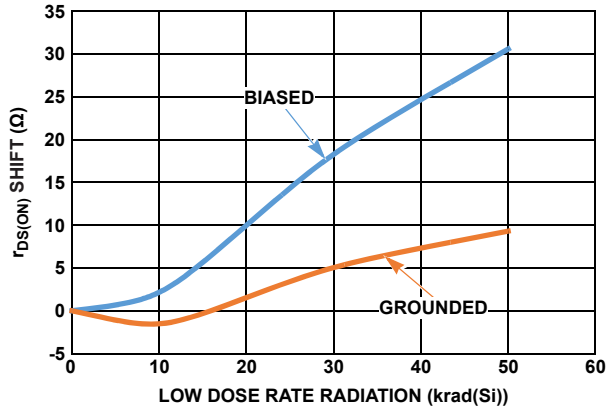


FIGURE 71. $r_{DS(ON)}$ SHIFT (V_{IN} = V^+) vs LDR RADIATION

Post Low Dose Rate Radiation Characteristics ($V\pm$ = ±12V)

Unless otherwise specified, $V\pm$ = ±12V, V_{CM} = 0,V_O = 0V, T_A = +25°C. This data is typical mean test data post radiation exposure at a low dose rate of <10mrad(Si)/s. This data is intended to show typical parameter shifts due to low dose rate radiation. These are not limits, nor are they guaranteed. **(Continued)**

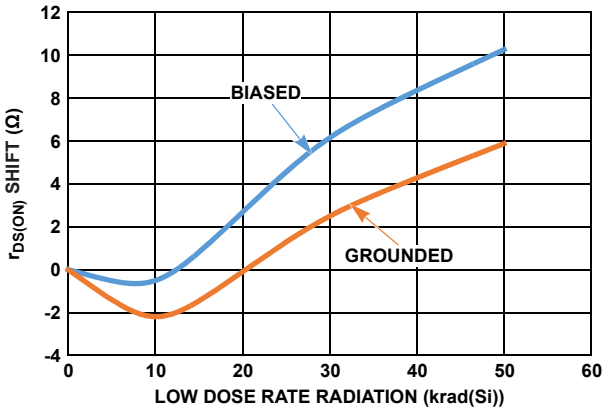


FIGURE 72. $r_{DS(ON)}$ SHIFT (V_{IN} = +5V) vs LDR RADIATION

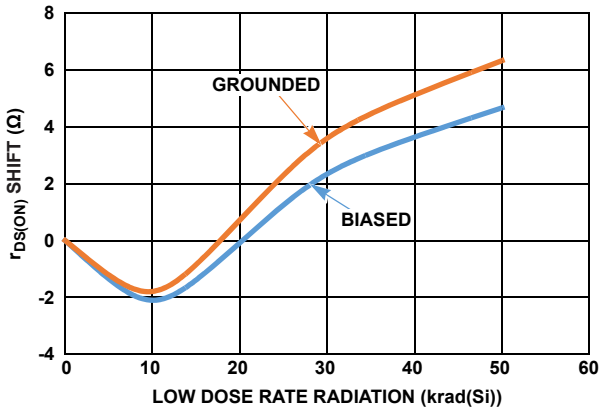


FIGURE 73. $r_{DS(ON)}$ SHIFT (V_{IN} = -5V) vs LDR RADIATION

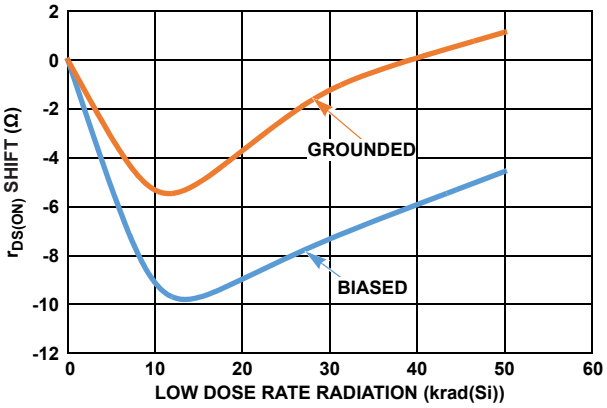


FIGURE 74. $r_{DS(ON)}$ SHIFT (V_{IN} = V^-) vs LDR RADIATION

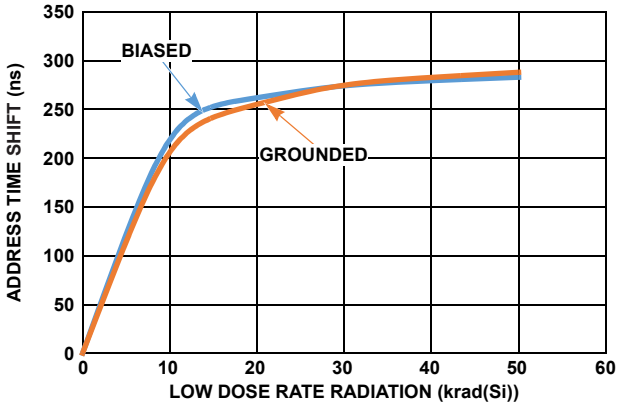


FIGURE 75. t_{ADD} SHIFT (LOW TO HIGH) vs LDR RADIATION

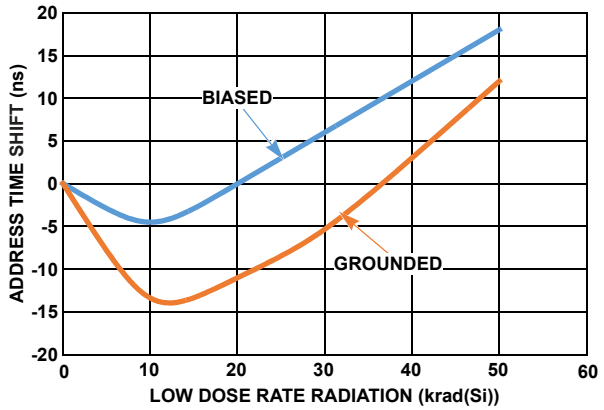


FIGURE 76. t_{ADD} SHIFT (HIGH TO LOW) vs LDR RADIATION

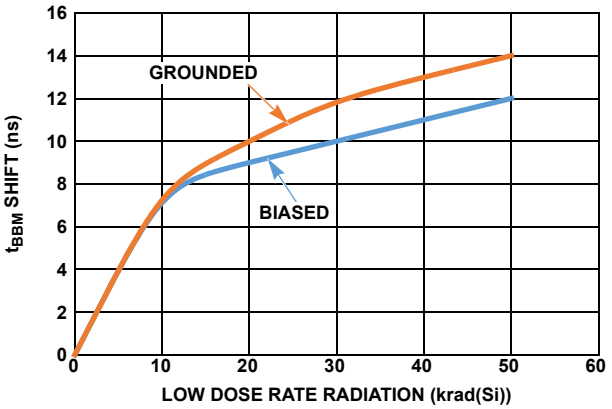


FIGURE 77. t_{BBM} SHIFT vs LDR RADIATION

Post Low Dose Rate Radiation Characteristics (V± = ±12V)

Unless otherwise specified, V± = ±12V, V_{CM} = 0,V_O = 0V, T_A = +25°C. This data is typical mean test data post radiation exposure at a low dose rate of <10mrad(Si)/s. This data is intended to show typical parameter shifts due to low dose rate radiation. These are not limits, nor are they guaranteed. **(Continued)**

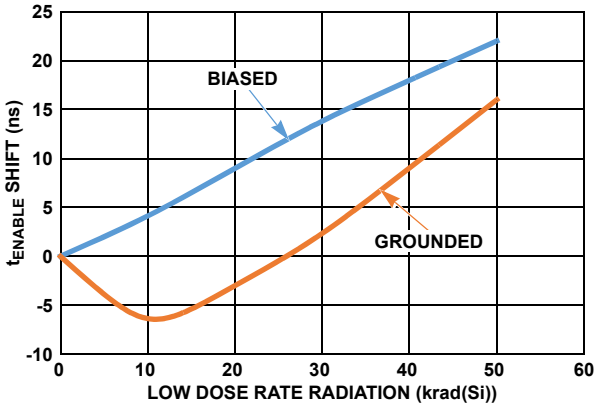


FIGURE 78. t_{ENABLE} SHIFT vs LDR RADIATION

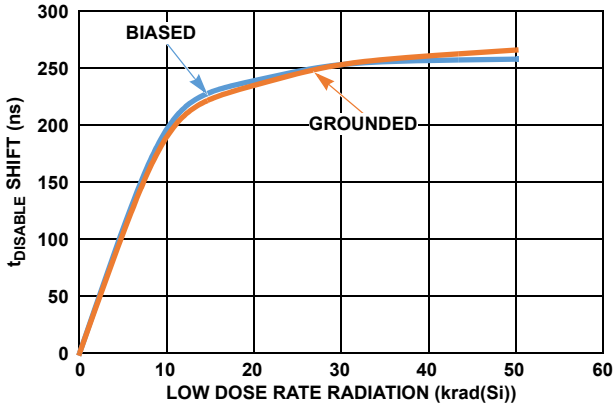


FIGURE 79. $t_{DISABLE}$ SHIFT vs LDR RADIATION

Applications Information

Power-Up Considerations

The circuit is designed to be insensitive to any given power-up sequence between V^+, V^-, and VREF; however, it is recommended that all supplies power up relatively close to each other.

Overvoltage Protection

The ISL71840SEH has overvoltage protection on both the input and the output. On the output, the voltage is limited to a diode past the rails. Each of the inputs has independent overvoltage protection that works regardless of the switch being selected. If a switch experiences an overvoltage condition (3V to 4V past the rail), the switch is turned off. As soon as the voltage returns within the rails, the switch returns to normal operation.

VREF and Logic Functionality

The VREF pin sets the logic threshold for the ISL71840SEH. The range for VREF is between 4.5V and 5.5V with a nominal voltage of 5V. The address pins and enable are compared against roughly 30% of V_{REF} voltage (refer to Figure 80). With 5V on V_{REF}, the switching point is set to around 1.4V. This switching point allows for both 5V and 3.3V logic control.

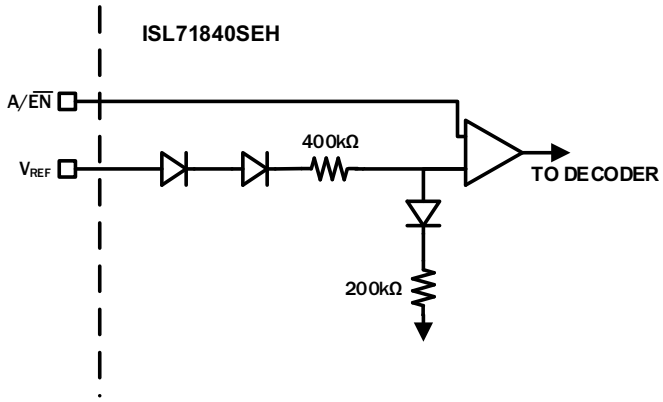


FIGURE 80. SIMPLIFIED V_{REF} CIRCUITRY

Considerations for Redundant Applications

When using the ISL71840SEH in a cold sparing application, it is recommended to keep the ground pin connected to system ground at all times. All supply pins (V+, V-, and VREF) should either be grounded or floating together.

If the supply pins are floating, it is recommended to place a high value bleed resistor (~1MΩ) in parallel with the decoupling capacitors on each supply pin to ensure that the supply voltage is discharged in a predictable manner. Figures 81 and 82 illustrate the recommended cold sparing setup for both shorted or floating supplies.

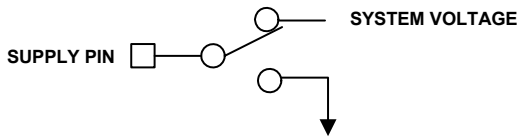


FIGURE 81. COLD SPARING SETUP WITH SUPPLIES SHORTED

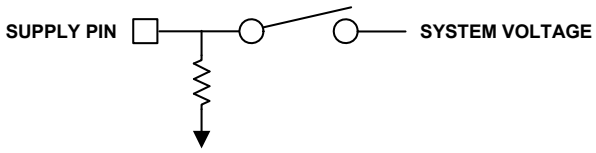


FIGURE 82. COLD SPARING SETUP WITH SUPPLIES FLOATING

ISL71840SEH vs ISL71841SEH

The ISL71841SEH, a 32-channel version of the ISL71840SEH, is available in a 48 Ld CQFP. The parts' performance specifications are very similar. Apart from the apparent increase in channel density, the ISL71841SEH has slightly higher output leakage compared to the ISL71840SEH because it has more channels connected to the output. The supply current for the ISL71841SEH is also slightly higher compared to the ISL71840SEH. Refer to Table 1 on page 3 for a comparison of the two devices.

Die Characteristics

Die Dimensions

2820µm x 4080µm (111 mils x 161 mils)
Thickness: 483µm ±25µm (19 mils ±1 mil)

Interface Materials

GLASSIVATION

Type: 12kÅ Silicon Nitride on 3kÅ Oxide

TOP METALLIZATION

Type: 300Å TiN on 2.8µm AlCu
In Bondpads, TiN has been removed.

BACKSIDE FINISH

Silicon

PROCESS

P6SOI

Assembly Related Information

SUBSTRATE POTENTIAL

Floating

Additional Information

WORST CASE CURRENT DENSITY

1.6×10^5 A/cm^2

TRANSISTOR COUNT

5682

Weight of Packaged Device

2.096 grams

Lid Characteristics

Finish: Gold
Potential: Grounded, tied to package Pin 12

Metalization Mask Layout

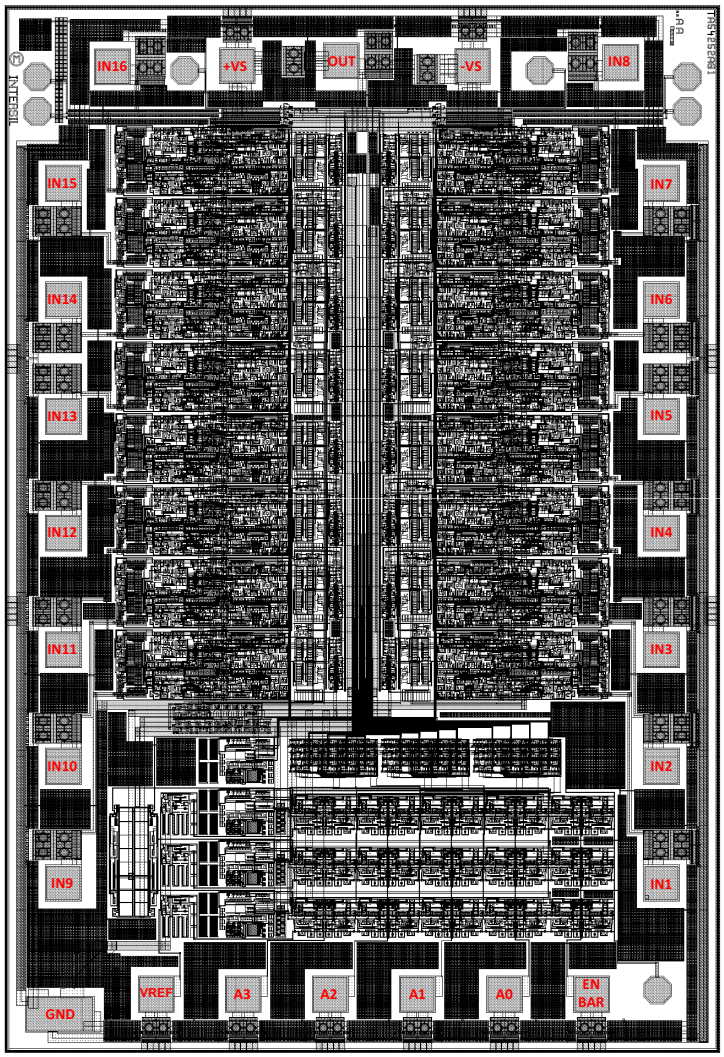


TABLE 3. ISL71840SEH DIE LAYOUT X-Y COORDINATES

PAD NUMBER	PAD NAME	PACKAGING PIN	ΔX (µm)	ΔY (µm)	X (µm)	Y (µm)
1	IN8	P26	127	127	979.5	1768.5
3	V-	P27	125	125	417.5	1754.5
4	OUT	P28	125	125	-79.5	1774.5
5	V+	P1	125	125	-474.5	1756.5
7	IN16	P4	127	127	-947.5	1752.5
10	IN15	P5	127	127	-1133.5	1310.5
11	IN14	P6	127	127	-1133.5	868.5
12	IN13	P7	127	127	-1133.5	426.5
13	IN12	P8	127	127	-1133.5	-15.5
14	IN11	P9	127	127	-1133.5	-457.5
15	IN10	P10	127	127	-1133.5	-899.5
16	IN9	P11	127	127	-1133.5	-1341.5
17	GND	P12	250	125	-1147	-1839.5
18	VREF	P13	127	127	-781.5	-1763.5
19	A3	P14	127	127	-451.5	-1763.5
20	A2	P15	127	127	-121.5	-1763.5
21	A1	P16	127	127	208.5	-1763.5
22	A0	P17	127	127	538.5	-1763.5
23	EN_B	P18	127	127	868.5	-1763.5
25	IN1	P19	127	127	1133.5	-1341.5
26	IN2	P20	127	127	1133.5	-899.5
27	IN3	P21	127	127	1133.5	-457.5
28	IN4	P22	127	127	1133.5	-15.5
29	IN5	P23	127	127	1133.5	426.5
30	IN6	P24	127	127	1133.5	868.5
31	IN7	P25	127	127	1133.5	1310.5

NOTE: Origin of coordinates is the center of the die.

Revision History

The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please go to the web to make sure that you have the latest revision.

DATE	REVISION	CHANGE
Aug 10, 2023	6.00	In ABS MAX RATINGS Section on page 5 changed "Digital Input Voltage Range ($\overline{EN}$, Ax) from "GND to V+" to "GND - 0.3V to +16.5V". Updates to the Electrical Specifications (±15V) table are as follows: • On page 5, for parameters Channel On-Resistance, r_{ON} Match Between Channels, and ON-Resistance Flatness added $V_{\overline{EN}}$ = 0V to the Test Conditions. • On page 6, for parameter Switch Off Leakage with Device Powered OFF changed it to Switch Off Leakage with Device Powered OPEN and updated test conditions. • On page 6, Added new parameter Switch On Leakage Current into the Drain (Overvoltage) specification. • On page 6, for parameter Switch On Leakage Current into the Source (Overvoltage), update the limits values and units to µA. • On page 6, for parameter Switch Off Leakage Current into the Source (Overvoltage), added a new T_A = -55°C specification. • On page 7, for parameter Switch On Leakage Current into the Source/Drain added $V_{\overline{EN}}$ = 0V to the Test Conditions. • Changed the I+, I- Quiescent & Standby Supply Current parameters to VREF = 5.5V, VIN = 0V, VA = 0.8V. • Changed parameter nomenclature for Supply Current Into V_{REF} to: Quiescent Supply Current Into V_{REF}. • Added new specification parameter Standby Current Into V_{REF}. Updates to the Electrical Specifications (±12V) table on page 8 are as follows: • For parameters Channel On-Resistance, r_{ON} Match Between Channels, and ON-Resistance Flatness added $V_{\overline{EN}}$ = 0V to the Test Conditions. • Changed the I+, I- Quiescent & Standby Supply Current parameters to VREF = 5.5V, VIN = 0V, VA = 0.8V. • Changed parameter nomenclature for Supply Current Into V_{REF} to Quiescent Supply Current Into V_{REF}. • Added new specification parameter Standby Current Into V_{REF}.
Oct 24, 2022	5.01	Removed Related Literature section. Updated links throughout. Updated Ordering information formatting and notes. Changed the "Metallization Mask Layout" diagram to correct label for pad number 18, from: A4, to: VREF. Changed "Table 3. ISL71840SEH DIE LAYOUT X-Y COORDINATES" the 2nd row, 2nd column entry from: V+, to: V- and the 4th row, 2nd column entry from: V-, to: V+.
Feb 23, 2018	5.00	Added "Considerations for Redundant Applications" on page 23. Removed About Intersil and updated disclaimer.
Nov 30, 2017	4.00	Updated Related Literature section. Added Notes 4 and 5 to the Ordering Information table on page 3. Added ESD circuit images in Figure 3 on page 4.
Jun 9, 2016	3.00	Updated Ordering information table on page 3 by updating first column and updating Note 3. Updated bolding in Electrical Specification table and added test conditions to the Break-Before-Make Delay, Enable Turn-On Time and Disable Turn-Off Time specifications. Changed from "V_S" to "V±" in the titles of the Typical Performance, Post High and Post Low Dose Rate Radiation Characteristics curve tables. Changed units from mA to µA for Figures 31, 32, 33, 43, 44, 45, 55, 56, 57, 67, 68, 69.
Mar 30, 2016	2.00	Updated the heading for the Low Dose Rate Radiation Characteristics (Vs = ±15V) table on page 19 in third sentence changed from "high" to "low". Updated the heading for the Low Dose Rate Radiation Characteristics (Vs = ±12V) table on page 21 in third sentence changed from "high" to "low".
Nov 12, 2015	1.00	Corrected ESD Specification references on page 5. Updated Crosstalk and Off Isolation minimum specifications on page 7. Updated VSS and VDD to V+ and V- in "Block Diagram" on page 10, "Metallization Mask Layout" on page 24, and Table 3 on page 25. Removed redundant specs from ±12V Table (V_{CTE}, V_{ISO}, V_{CT}, C_A, C_{IN}, C_{OUT}). Added Figures 26, 28 and 30. Updated Figures 33 and 45 y-axis scale. Updated Figures 31 through 78 y-axis labels. Updated top metalization thickness and composition on page 24. Updated probe coordinates table for consistency on page 25.

Revision History

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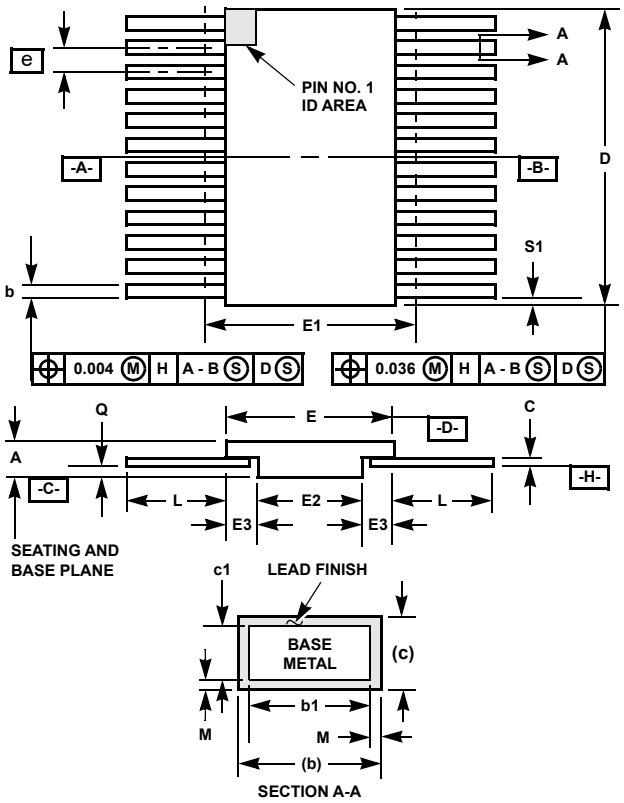
DATE	REVISION	CHANGE
Jun 15, 2015	0.00	Initial release

Package Outline Drawing

For the most recent package outline drawing, see K28.A.

Ceramic Metal Seal Flatpack Packages (Flatpack)



K28.A MIL-STD-1835 CDFP3-F28 (F-11A, CONFIGURATION B)
28 LEAD CERAMIC METAL SEAL FLATPACK PACKAGE

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.045	0.115	1.14	2.92	-
b	0.015	0.022	0.38	0.56	-
b1	0.015	0.019	0.38	0.48	-
c	0.004	0.009	0.10	0.23	-
c1	0.004	0.006	0.10	0.15	-
D	-	0.740	-	18.80	3
E	0.460	0.520	11.68	13.21	-
E1	-	0.550	-	13.97	3
E2	0.180	-	4.57	-	-
E3	0.030	-	0.76	-	7
e	0.050 BSC		1.27 BSC		-
k	0.008	0.015	0.20	0.38	2
L	0.250	0.370	6.35	9.40	-
Q	0.026	0.045	0.66	1.14	8
S1	0.00	-	0.00	-	6
M	-	0.0015	-	0.04	-
N	28		28		-

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NOTES:

1. Index area: A notch or a pin one identification mark shall be located adjacent to pin one and shall be located within the shaded area shown. The manufacturer's identification shall not be used as a pin one identification mark. Alternately, a tab (dimension k) may be used to identify pin one.
2. If a pin one identification mark is used in addition to a tab, the limits of dimension k do not apply.
3. This dimension allows for off-center lid, meniscus and glass overrun.
4. Dimensions b1 and c1 apply to lead base metal only. Dimension M applies to lead plating and finish thickness. The maximum limits of lead dimensions b and c or M shall be measured at the centroid of the finished lead surfaces, when solder dip or tin plate lead finish is applied.
5. N is the maximum number of terminal positions.
6. Measure dimension S1 at all four corners.
7. For bottom-brazed lead packages, no organic or polymeric materials shall be molded to the bottom of the package to cover the leads.
8. Dimension Q shall be measured at the point of exit (beyond the meniscus) of the lead from the body. Dimension Q minimum shall be reduced by 0.0015 inch (0.038mm) maximum when solder dip lead finish is applied.
9. Dimensioning and tolerancing per ANSI Y14.5M - 1982.
10. Controlling dimension: INCH.

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